

# Defect Sinks and Their Reactions

K.G. Field<sup>1,a</sup>,

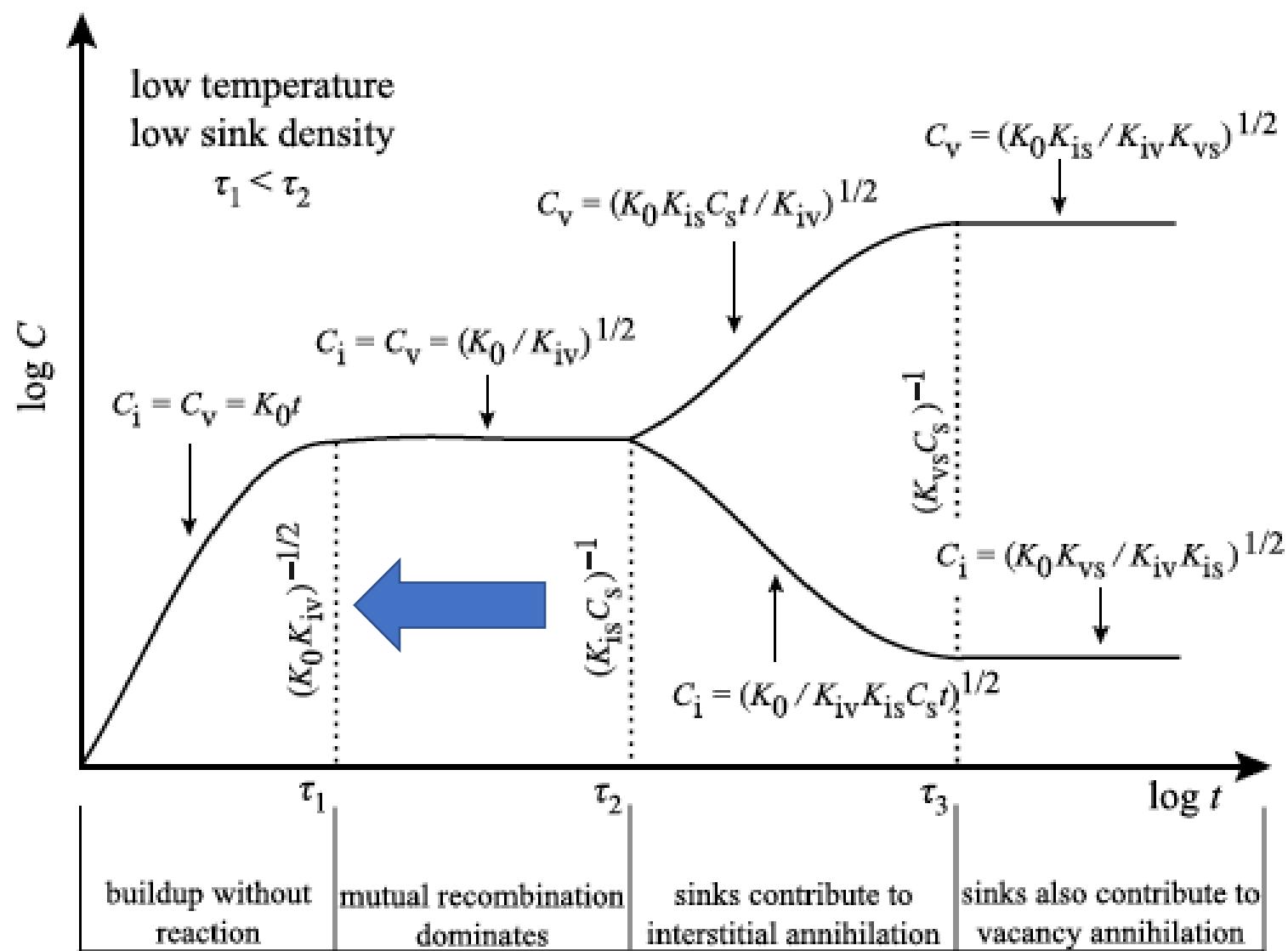
<sup>a</sup> kgfield@umich.edu

<sup>1</sup>University of Michigan

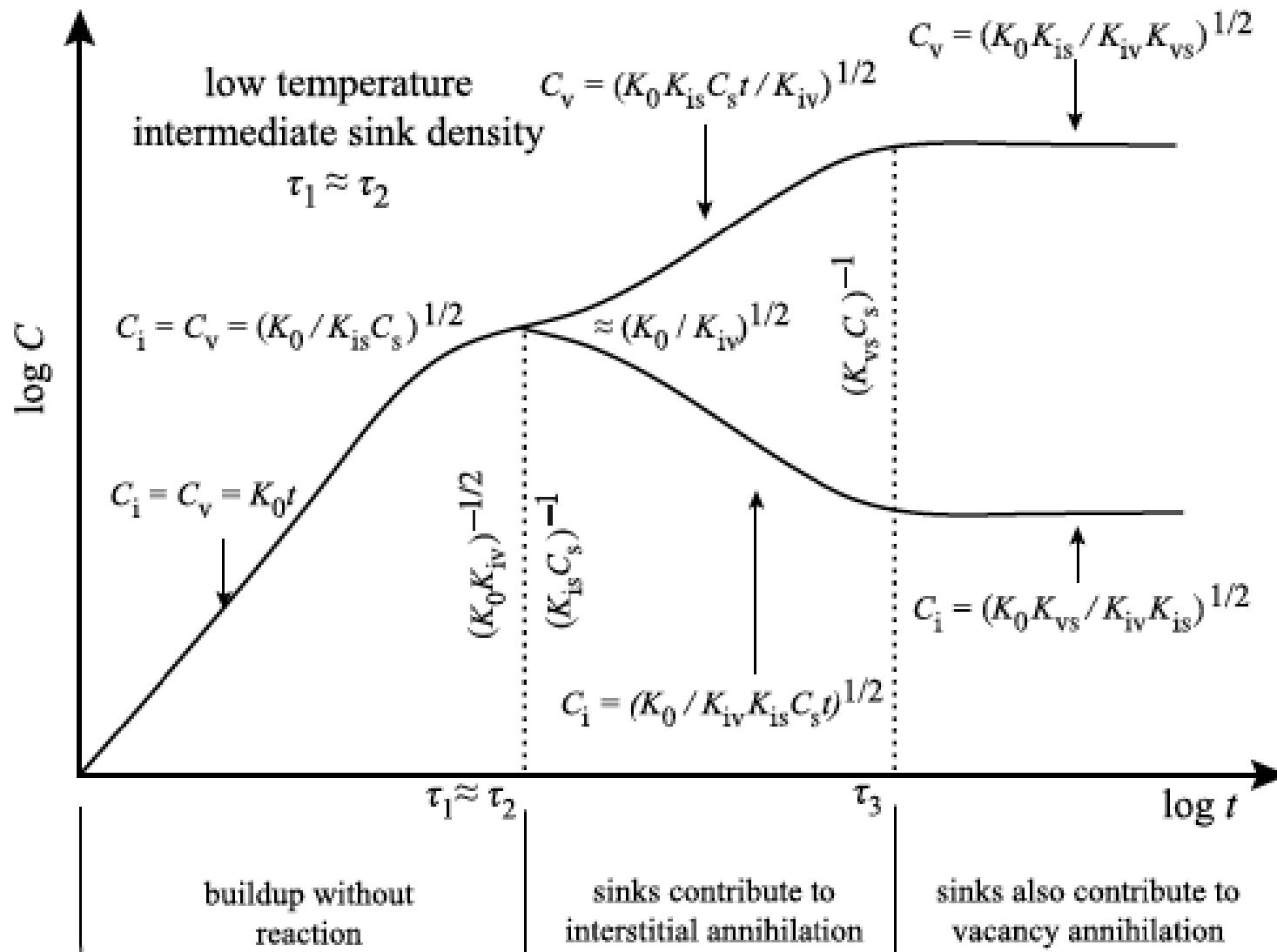


NUCLEAR ENGINEERING &  
RADIOLOGICAL SCIENCES  
UNIVERSITY OF MICHIGAN

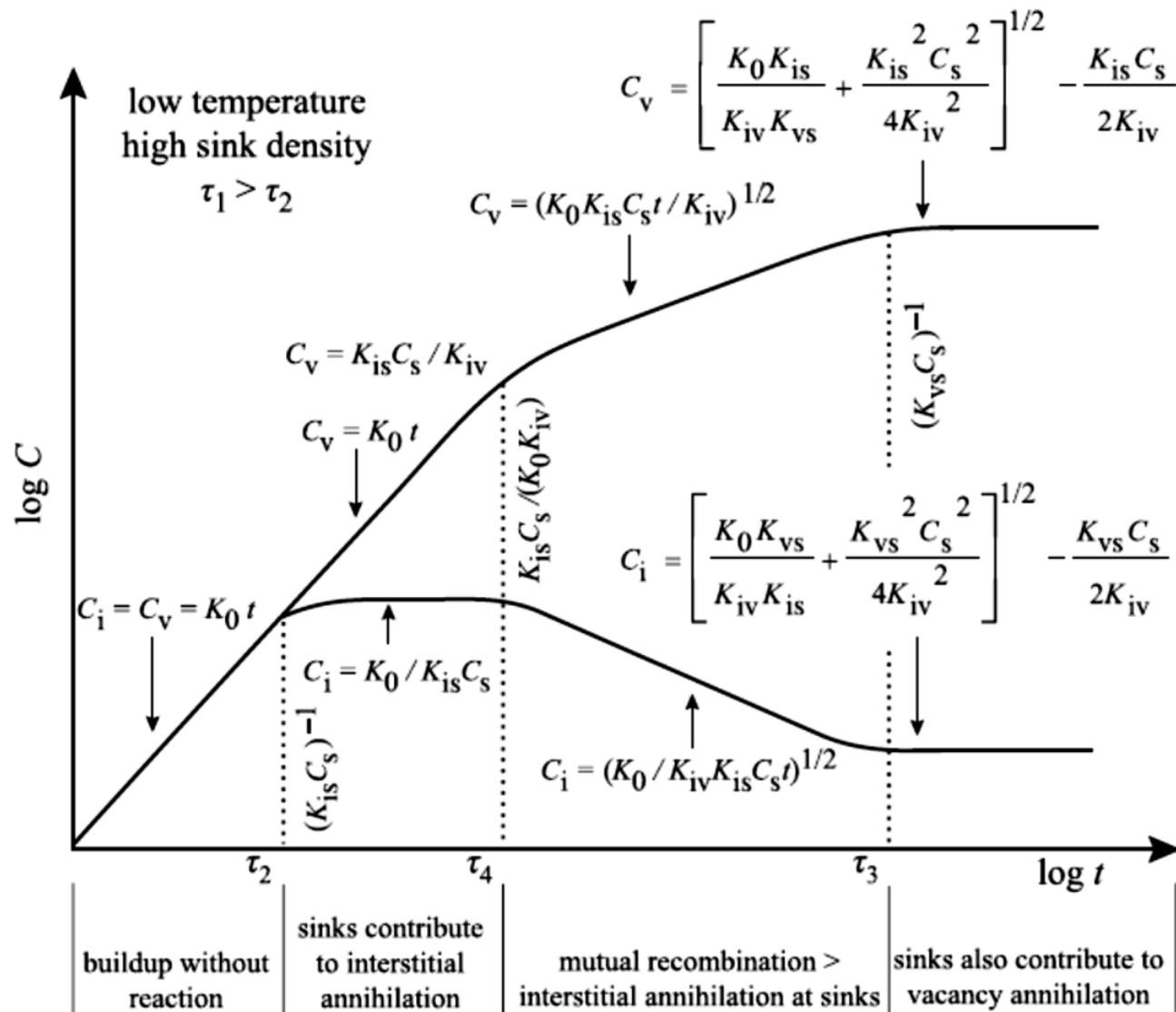
# Low Temperature, Increasing Sink Density



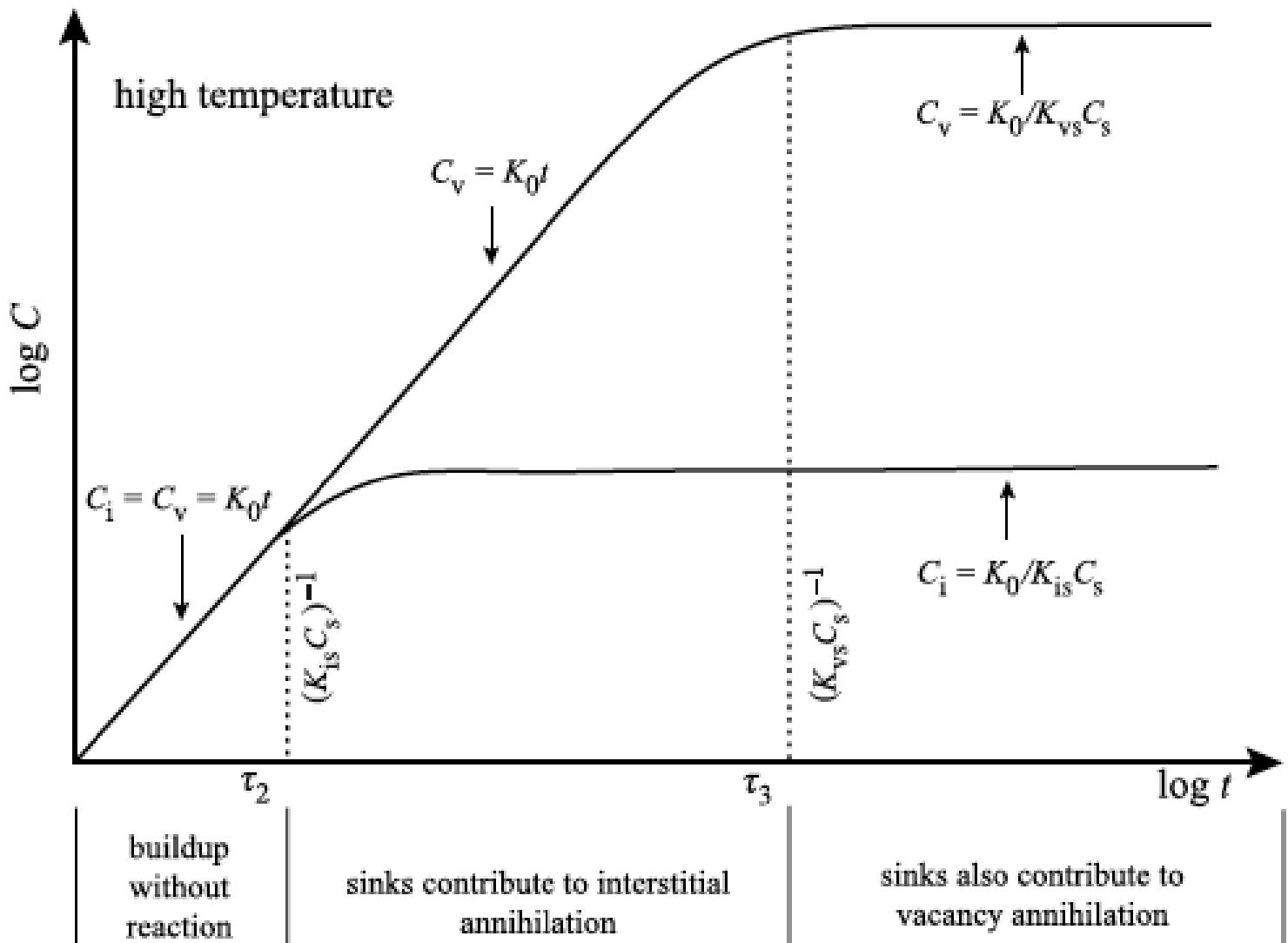
# Low Temperature, Increasing Sink Density



# Low T, High $C_s$



# High Temperature



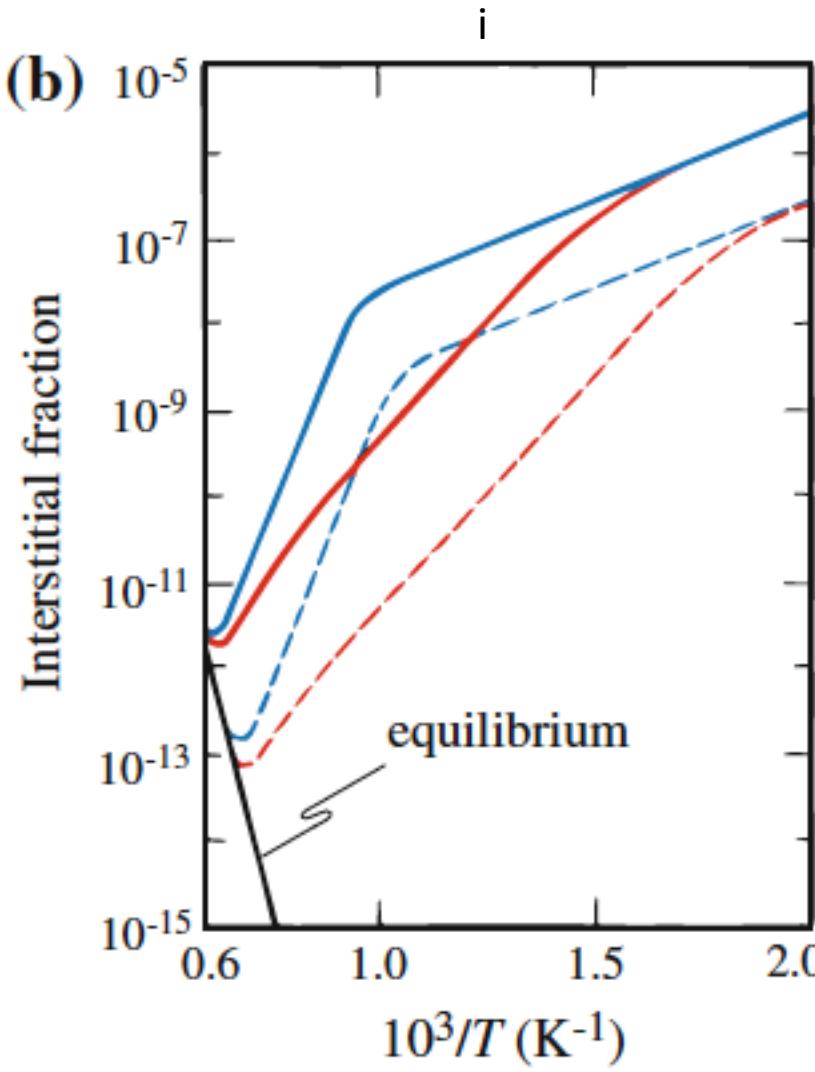
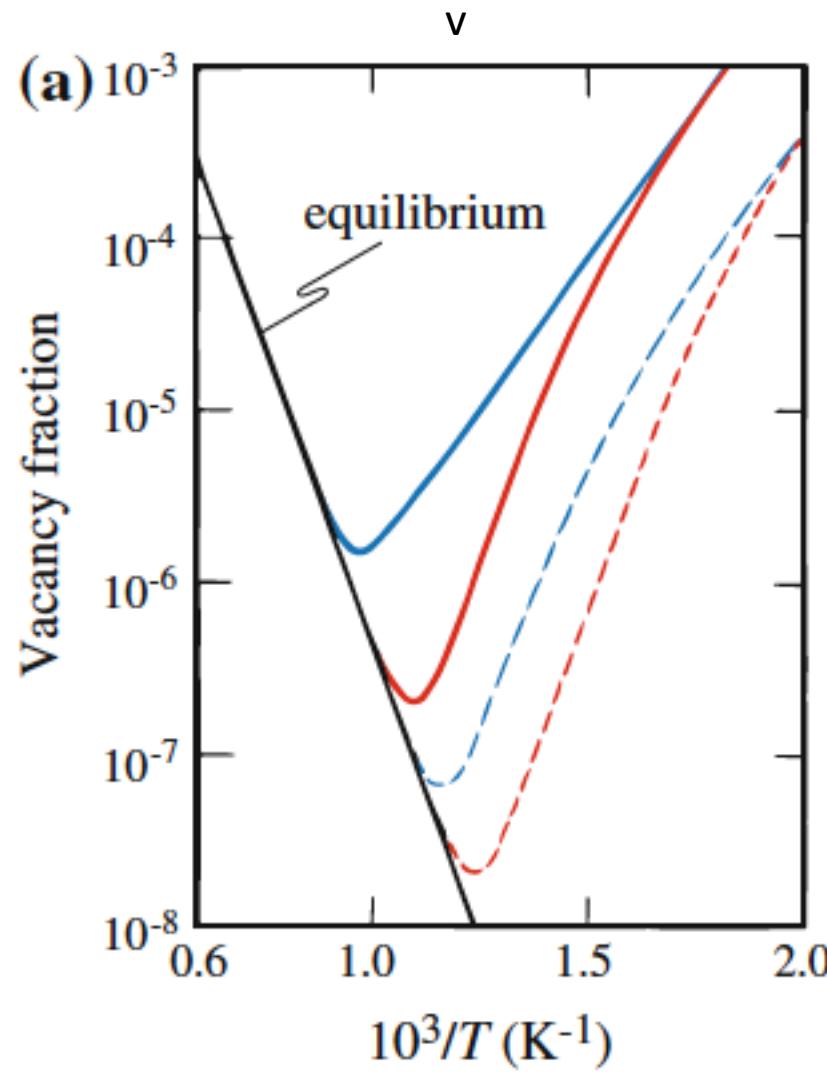
# Note on vacancy concentration

- $C_v$  must be accounted for thermal vacancies:
- Why are we ignoring this for interstitials?!

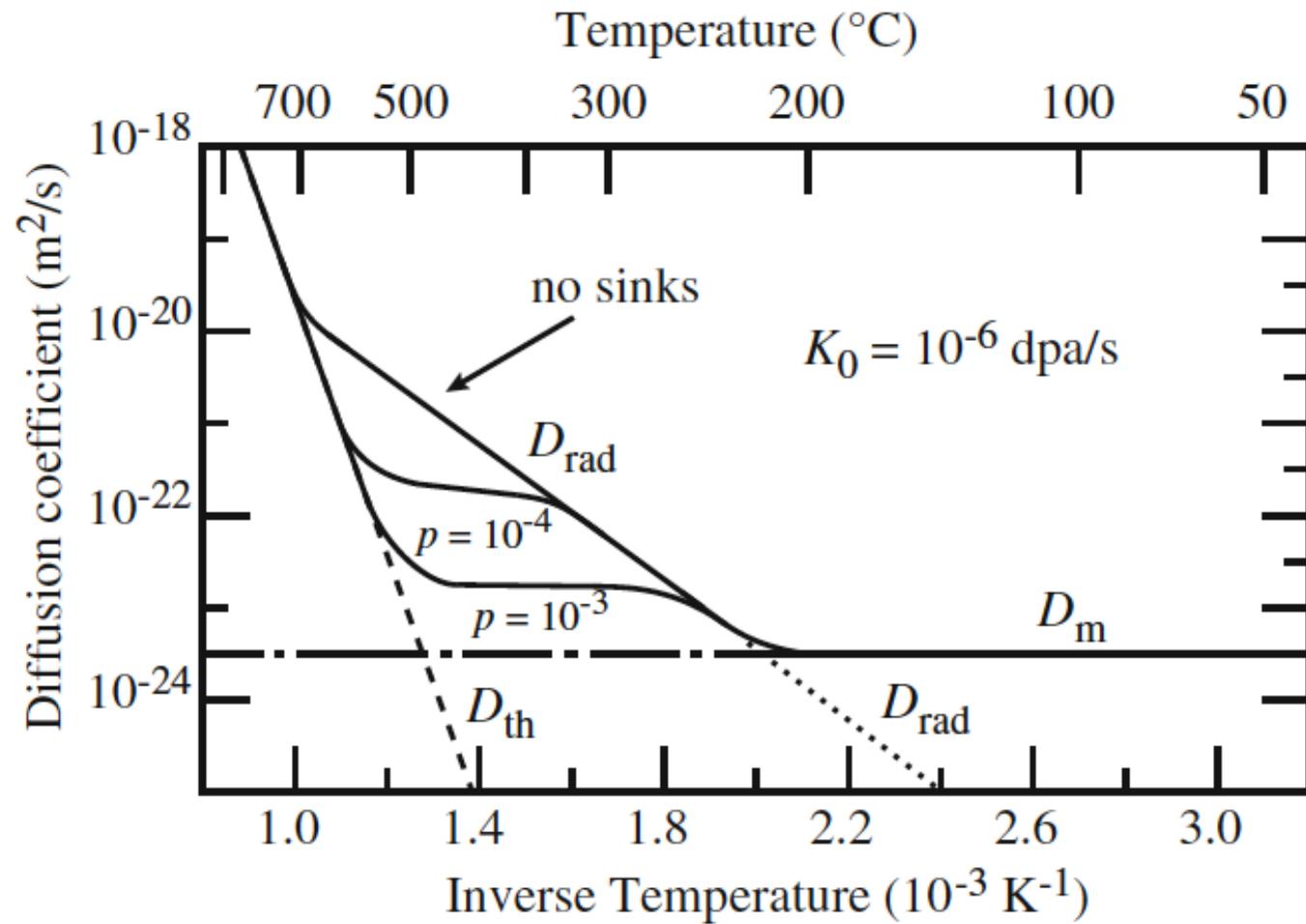


# Pulling this now together:

upper solid line — K<sub>0</sub> high ρ low  
lower solid line — K<sub>0</sub> high ρ high  
upper dashed line - - K<sub>0</sub> low ρ low  
lower dashed line - - - K<sub>0</sub> low ρ high



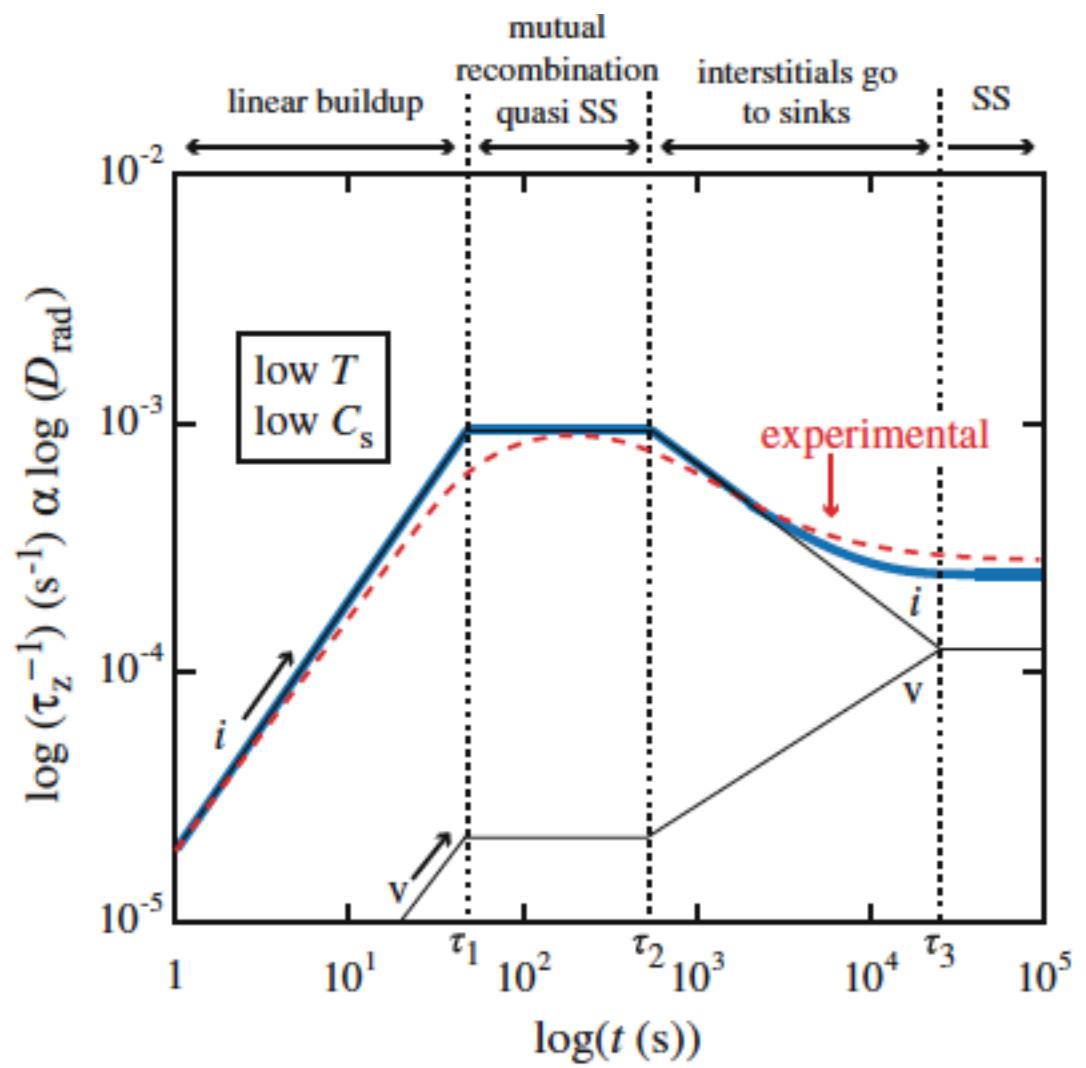
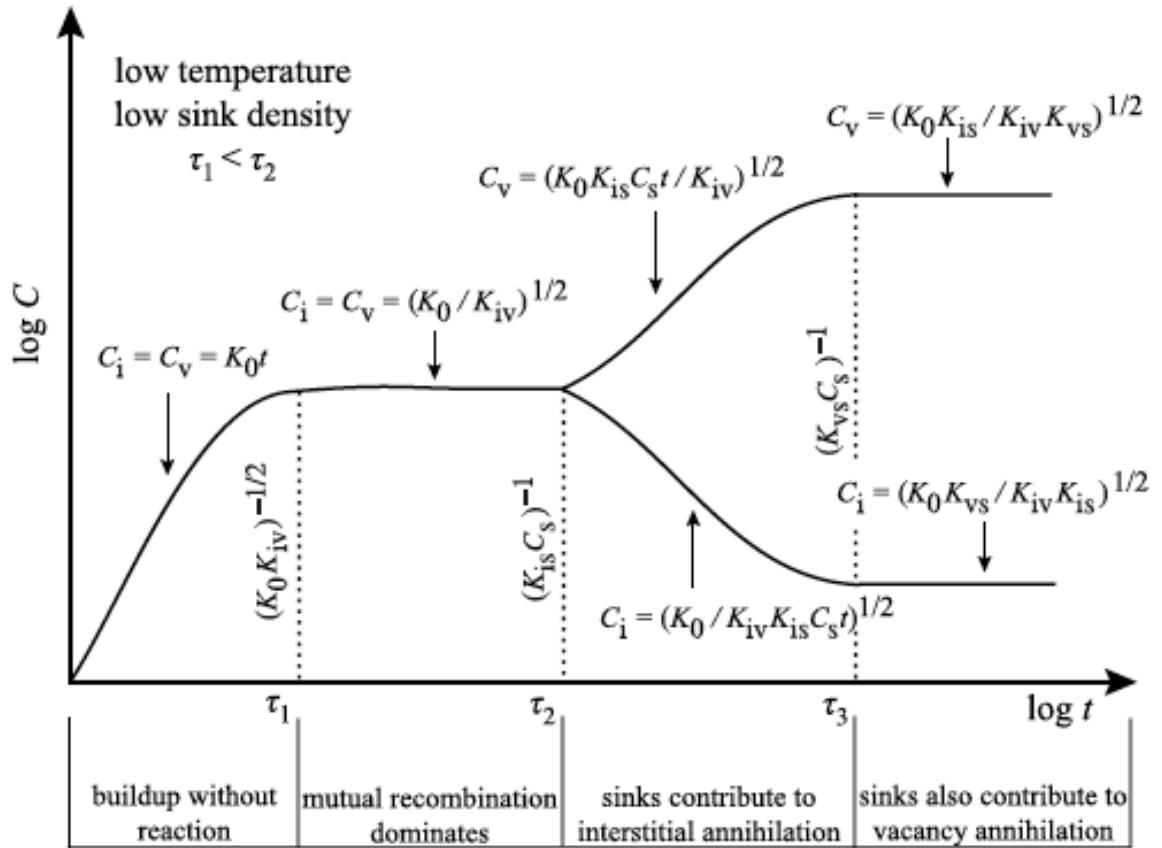
# Pulling this now together:



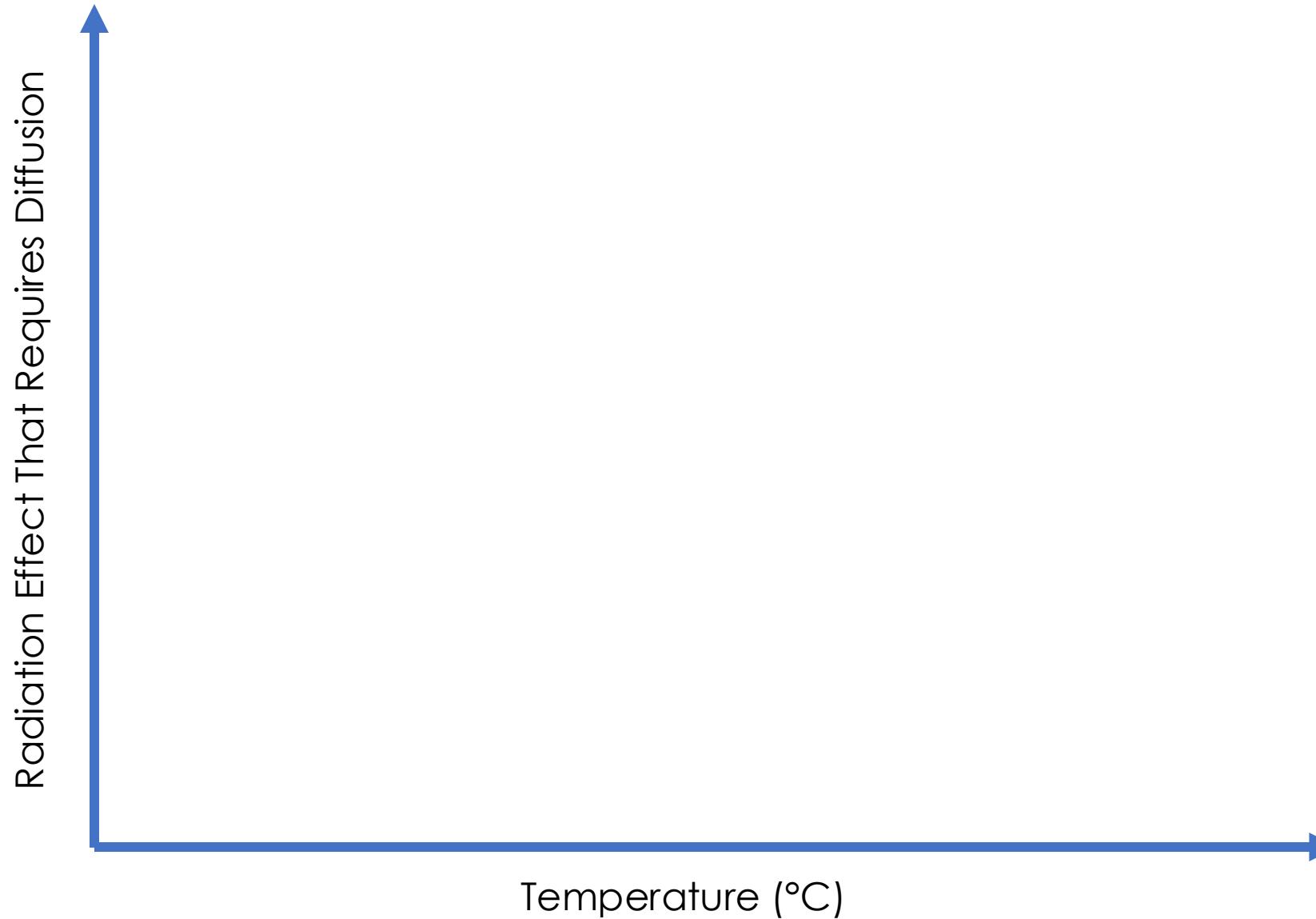
For systems where atoms can migrate both via interstitials and vacancies:

$$D_{\text{rad}} = D_v C_v + D_i C_i$$

# Pulling this now together:



# Thought Experiment: What should the shape of the magnitude of a radiation diffusion dependent response be?





This historic landmark, the oldest continuously operating cider mill in Michigan, first opened its doors the same year the Statue of Liberty was dedicated in New York Harbor. In what year did the Dexter Cider Mill begin pressing apples?



NUCLEAR ENGINEERING &  
RADIOLOGICAL SCIENCES  
UNIVERSITY OF MICHIGAN

# Rate of Reaction

- We have now determined the relative change of  $C_i$  and  $C_v$ , but the **rates are dependent on the reaction rate constant  $K_{AB}$  ( $s^{-1}$ )**, where the rate of reaction between A & B is:

$$K_{AB} C_A C_B \text{ reactions/cm}^3 s$$

- Analogous to first order chemical reactions
- We will consider two types of reactions:
  - Defect-defect reactions
  - Defect-extended sinks reactions

# Reaction Rate vs. Sink Strength

- Reaction Rate ( $K_{jX}$ , s<sup>-1</sup>): Describe the reaction between a point defect and sink
  - j: mobile point defect
  - X: the sink
  - Includes the diffusion coefficient, thus dependent on temperature, defect geometry, migration path, etc.
- Sink Strength ( $k_j^2$ , cm<sup>-2</sup>): The affinity (or "strength") of a sink to accept defects
  - Independent of defect properties (e.g. diffusion)
  - Square indicates that the rate constant for absorption to sinks is always positive

# Point-defect reactions with extended sinks

- To a *first approximation*, sinks act as “perfect” sinks
- In a perfect sink, all defects “stick” completely to the sink and never leak the sink -> think of these as black holes!
  - Result is the point-defect concentration at the surface of the sink is zero
- The rate of defect absorption at a sink,  $S$ , is then:
- The sink strength describes the strength or affinity of a sink for defects and is measured in  $[\text{length}^{-2}]$ . Physically,  $k_j^{-1}$  is the mean distance a free defect of type  $j$  travels in the solid before becoming trapped.
- For discussion, we will assume unsaturable sinks

# Sink types

- Sinks can behave differently:

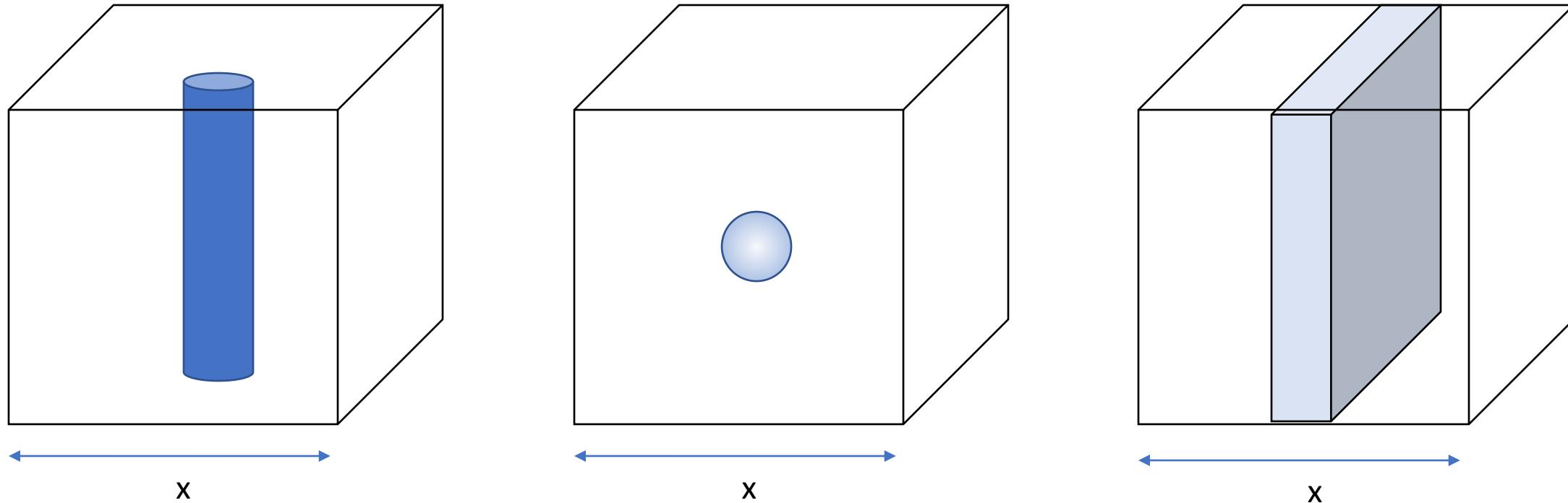
- Neutral (unbiased) sinks:

- Biased sinks:

- Variable (traps) sinks

# A simple thought experiment for $K_{vs}/K_{is}$

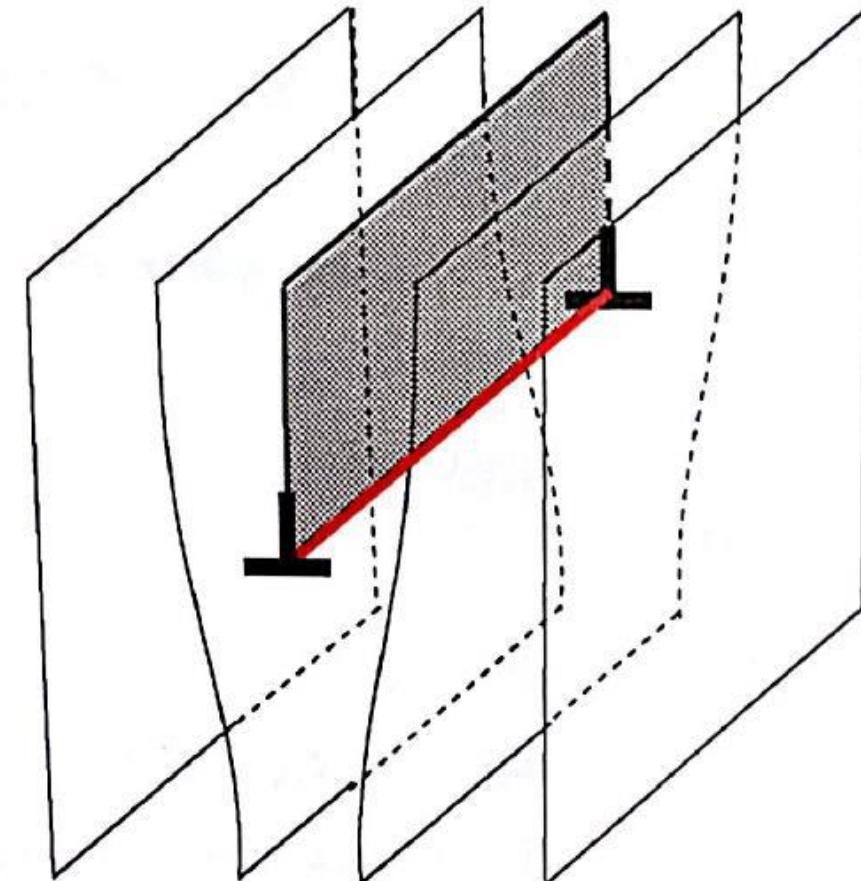
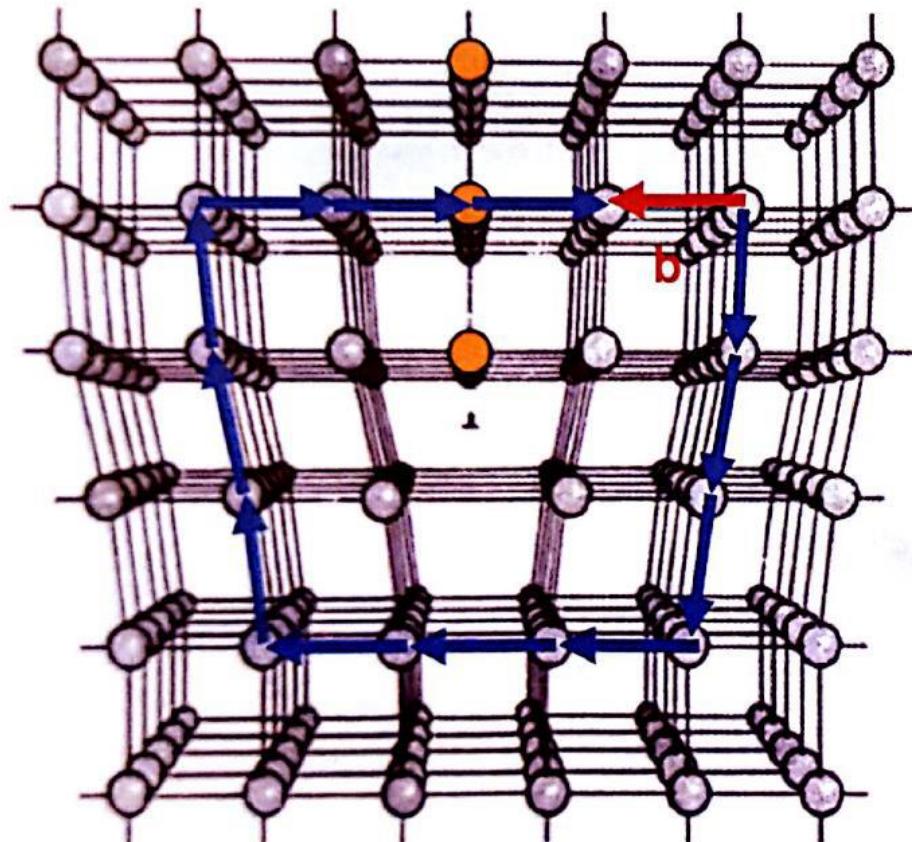
- Assume unbiased defect sink, radius/length of interaction is  $10a_0$



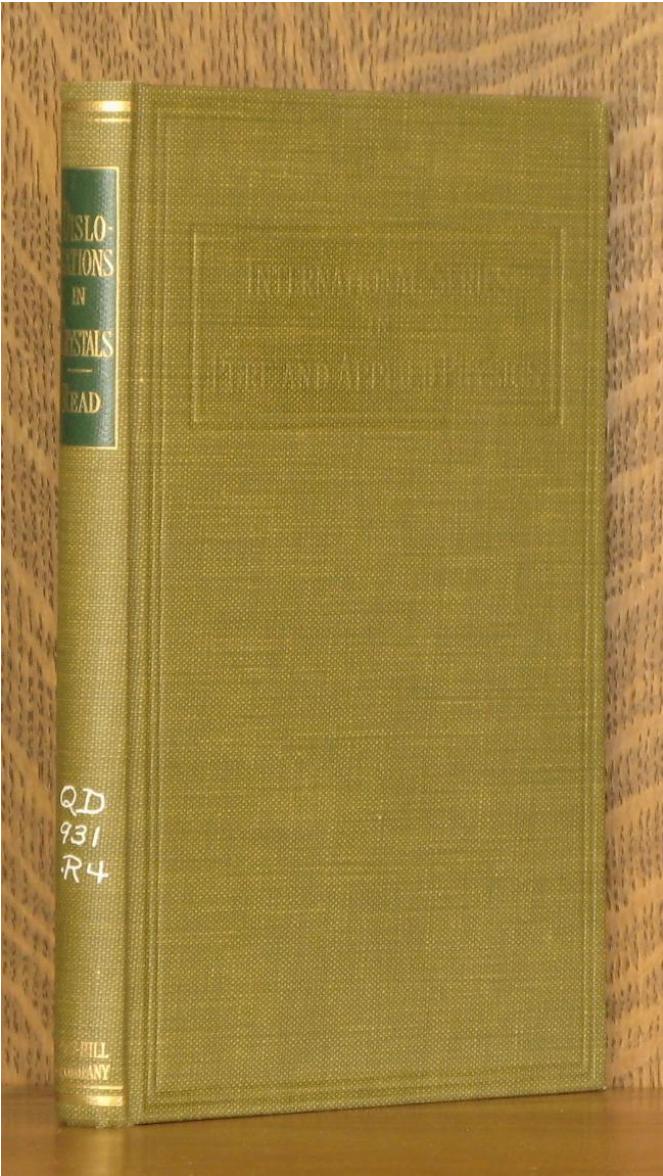
What sink will have the highest reaction rate (e.g. sink strength)?

# Sink Type I - Dislocations

- Linear defect
- Edge dislocation is an additional half plane of atoms
- Burgers vector and slip plane defines dislocation



This section on dislocations could be a whole book and class...



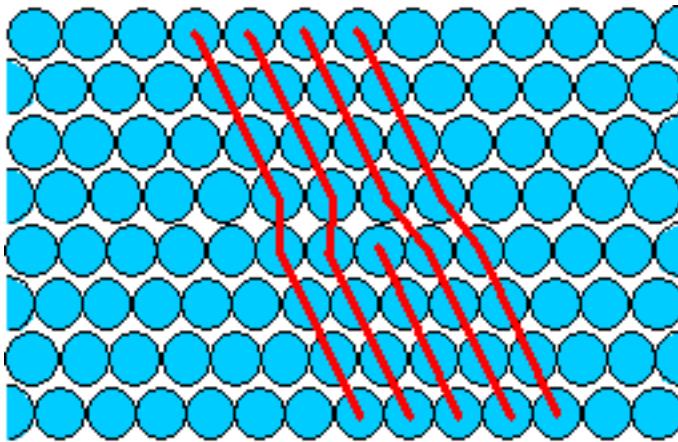
# What is a dislocation – a simple 2D picture

- “Old school” method to visualize dislocations:

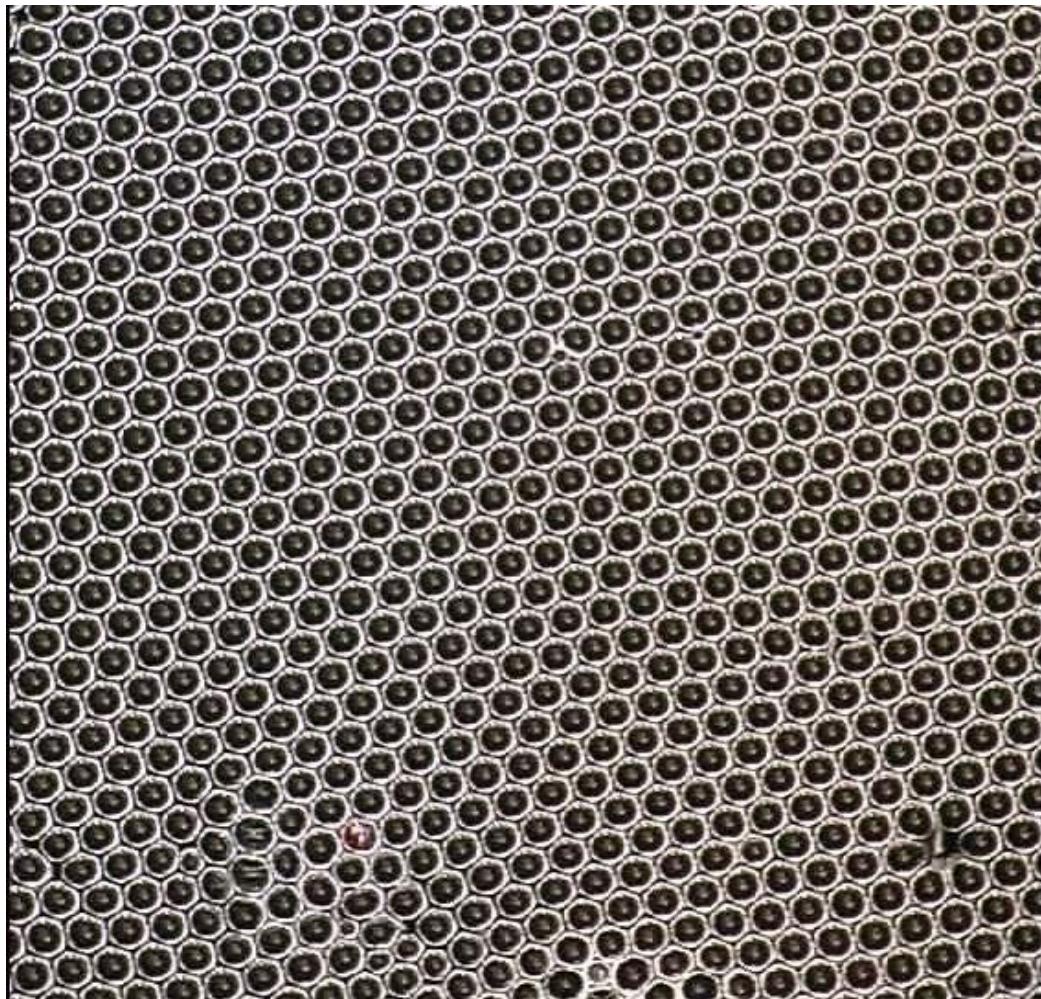


→ **Bubble rafts**

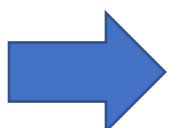
# What is a dislocation – a simple 2D picture



A dislocation in a 2D close-packed plane can be described as an extra 'half-row' of atoms in the structure. Dislocations can be characterized by the Burgers vector which gives information about the orientation and magnitude of the dislocation



Bubble raft that contains defects



# Dislocations are commonly observed using transmission electron microscopy (TEM)

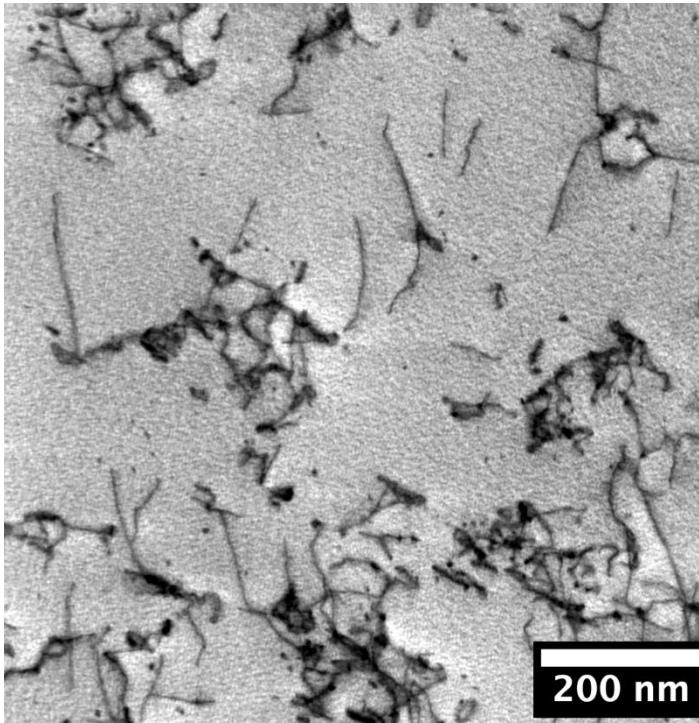
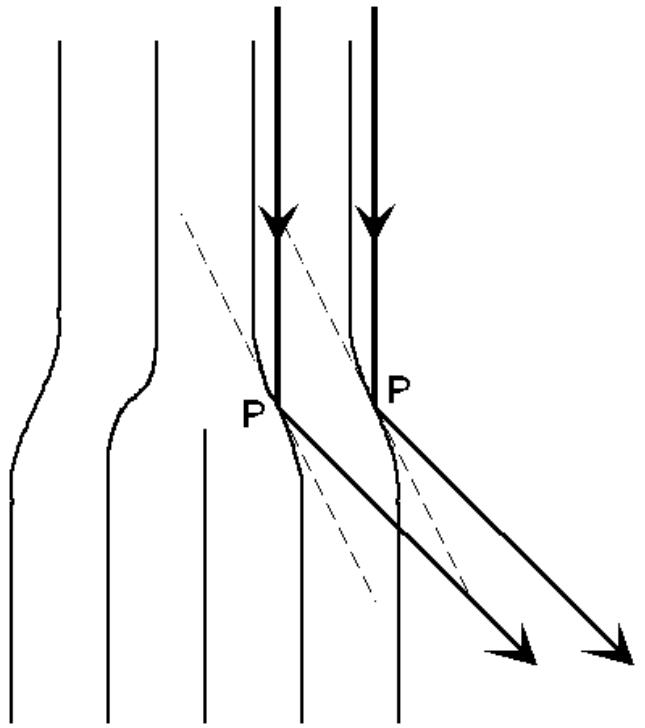
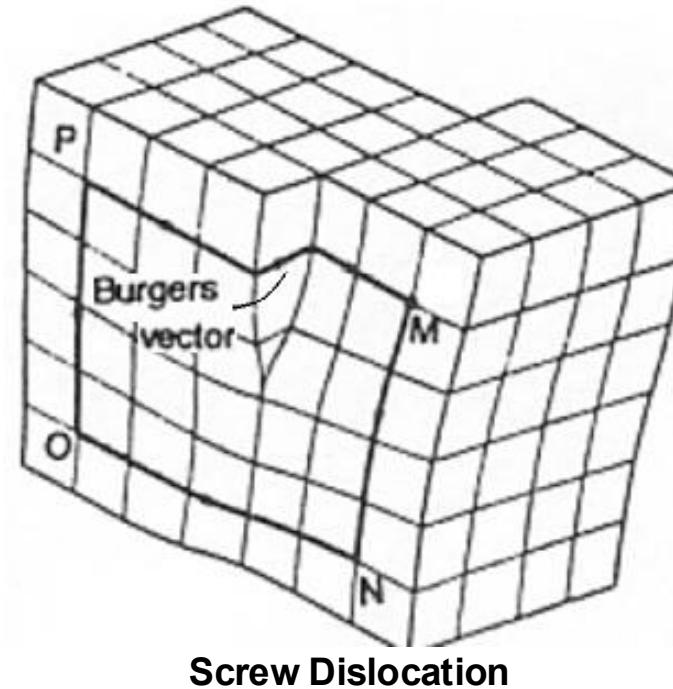
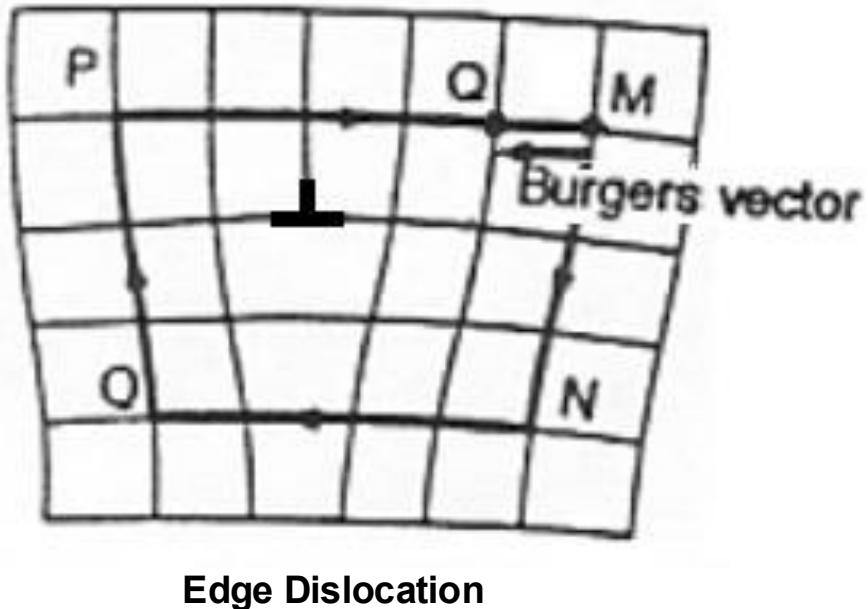


Image showing line dislocations (black contrast) in an accident tolerant FeCrAl alloy after cold working but before irradiation. Image taken using on-zone [100] Scanning Transmission Electron Microscopy (STEM) technique.

From: Your professor :0)

Dislocations can be observed in TEM due to the lattice distortion around the dislocation core resulting in Bragg diffraction of the electron beam

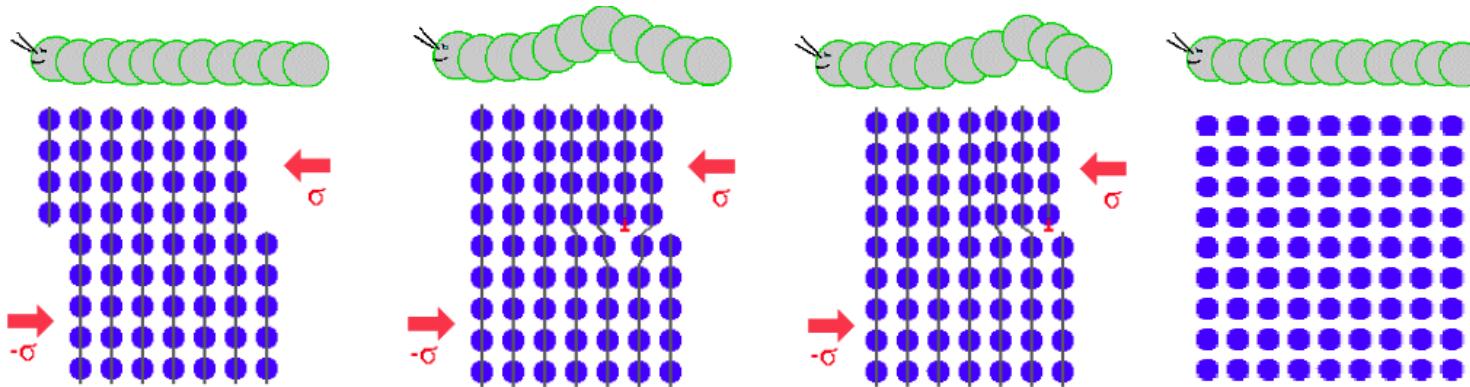
# Sink Type I - Dislocations



- Three types: Edge, Screw, and Mixed
  - Edge dislocation: line is perpendicular to the Burgers vector
  - Screw dislocation: line is parallel to Burgers vector
  - Mixed dislocations: a combination of edge and screw characteristics

# Sink Type I - Dislocations

- Dislocation motion is the primary form of deformation in a material



- Anything which impedes dislocation motion will strengthen the material, but may make it brittle

- Defects which impede dislocation motion:
  - Other dislocations
  - Interstitials
  - Impurities
  - Grain boundaries
  - Etc...

# Dislocation motion is the primary form of deformation in a material

← Stress



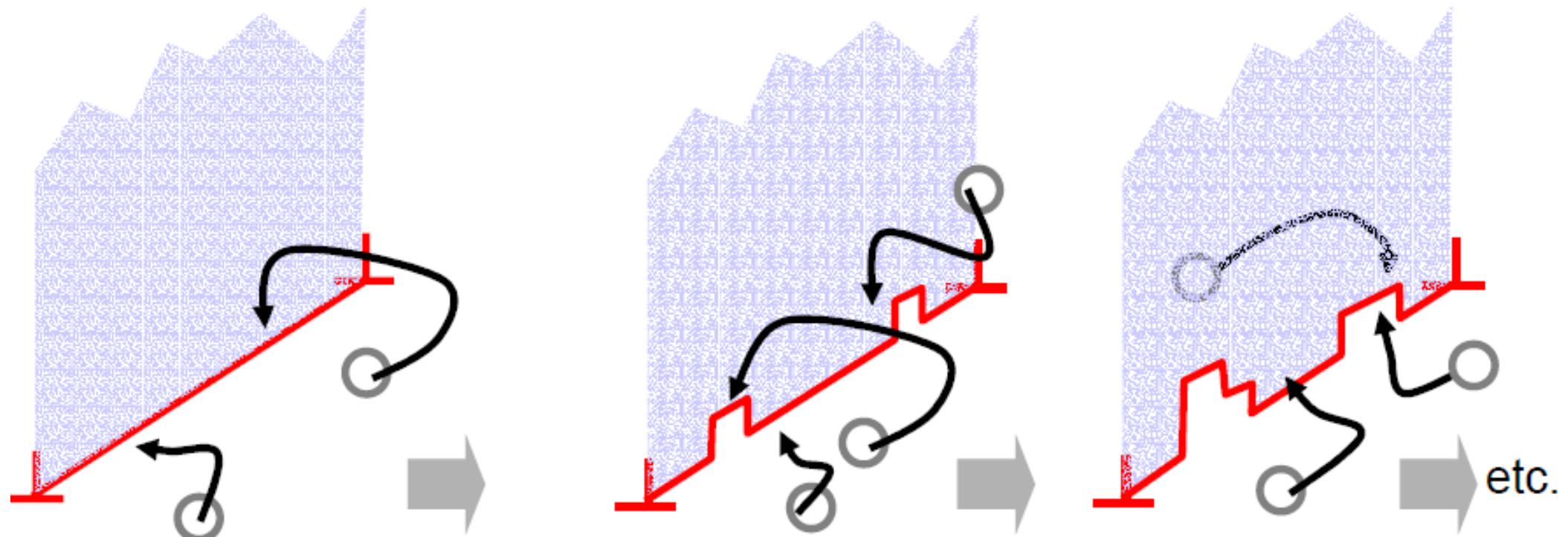
Video of bubble raft undergoing sheer stresses leading to dislocation motion and deformation

From:

<https://www.doitpoms.ac.uk/tplib/dislocations/videos/shear-stresses.mp4>

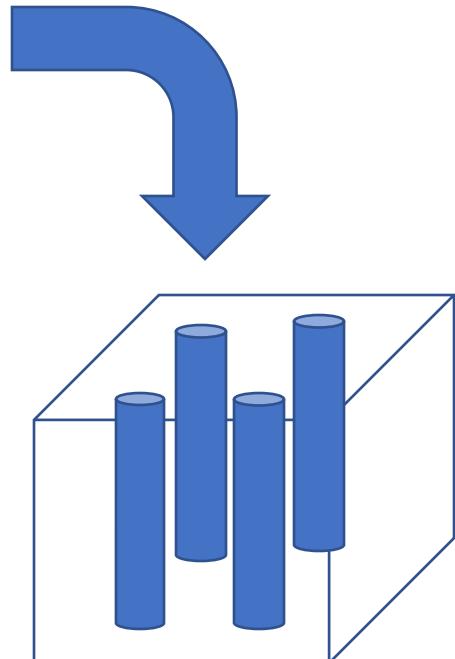
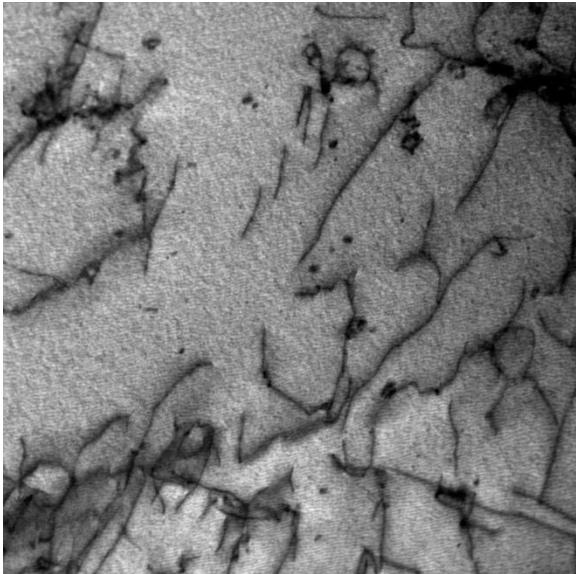
# Sink Type I - Dislocations

- Dislocation climb by vacancy absorption
- Leads to irradiation glide and creep



# Point Defect Absorption by Dislocations

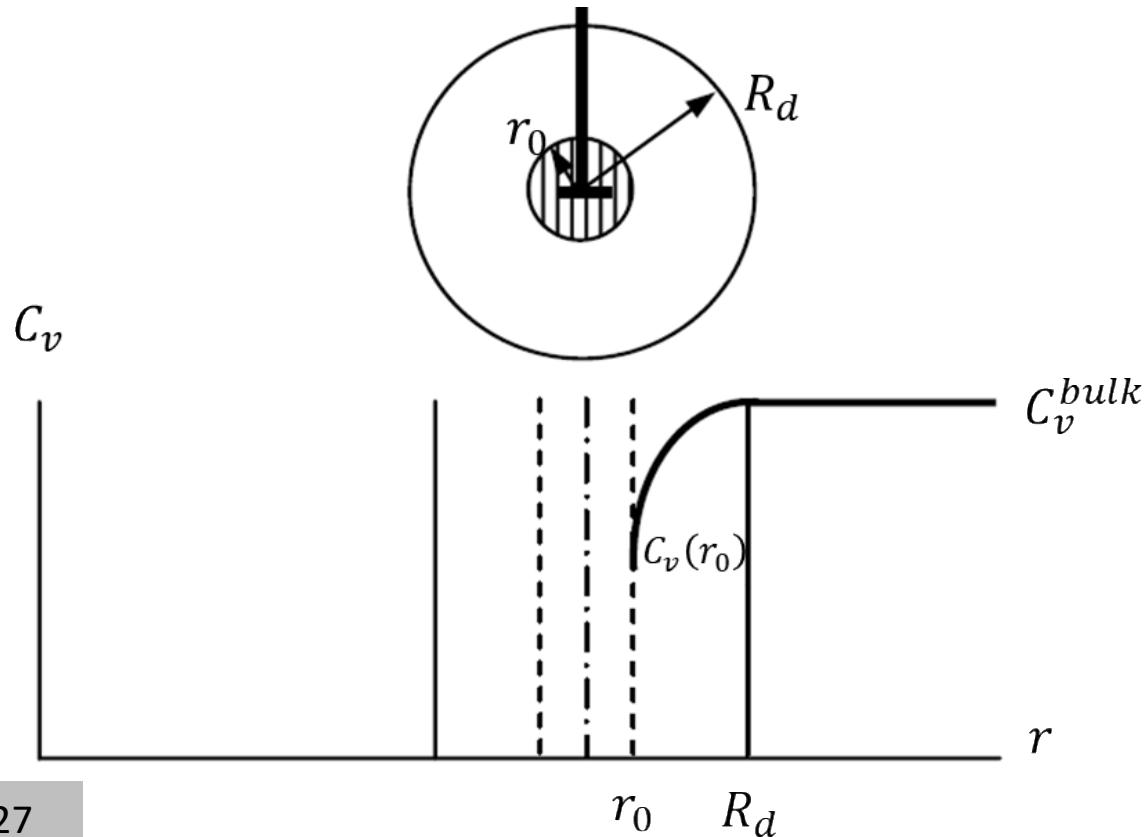
- Net reduction of strain energy
- Absorption leads to jog formation and climb



- Assumptions to determine rate of absorption
  - Even distribution of dislocation line density ( $p_d$  – cm<sup>-2</sup>)
  - Only one type of dislocation defect
  - Defects enter but do not exit the dislocation core  $r_0$
  - At a distance  $R_d$  the concentration of defects is equal to  $C_{i,v}^{bulk}$
  - No influence of the dislocation strain field

# Point Defect Absorption by Dislocations

- Net reduction of strain energy
- Absorption leads to jog formation and climb



- Assumptions to determine rate of absorption
  - Even distribution of dislocation line density ( $\mathbf{p}_d - \text{cm}^{-2}$ )
  - Only one type of dislocation defect
  - Defects enter but do not exit the dislocation core  $r_0$
  - At a distance  $R_d$  the concentration of defects is equal to  $C_{i,v}^{bulk}$
  - No influence of the dislocation strain field

# Point Defect Absorption by Dislocations

- Our steady state assumption gives (in radial coordinates):

$$\frac{1}{r} \frac{d}{dr} \left( r \frac{dC_{i,v}}{dr} \right) = 0$$

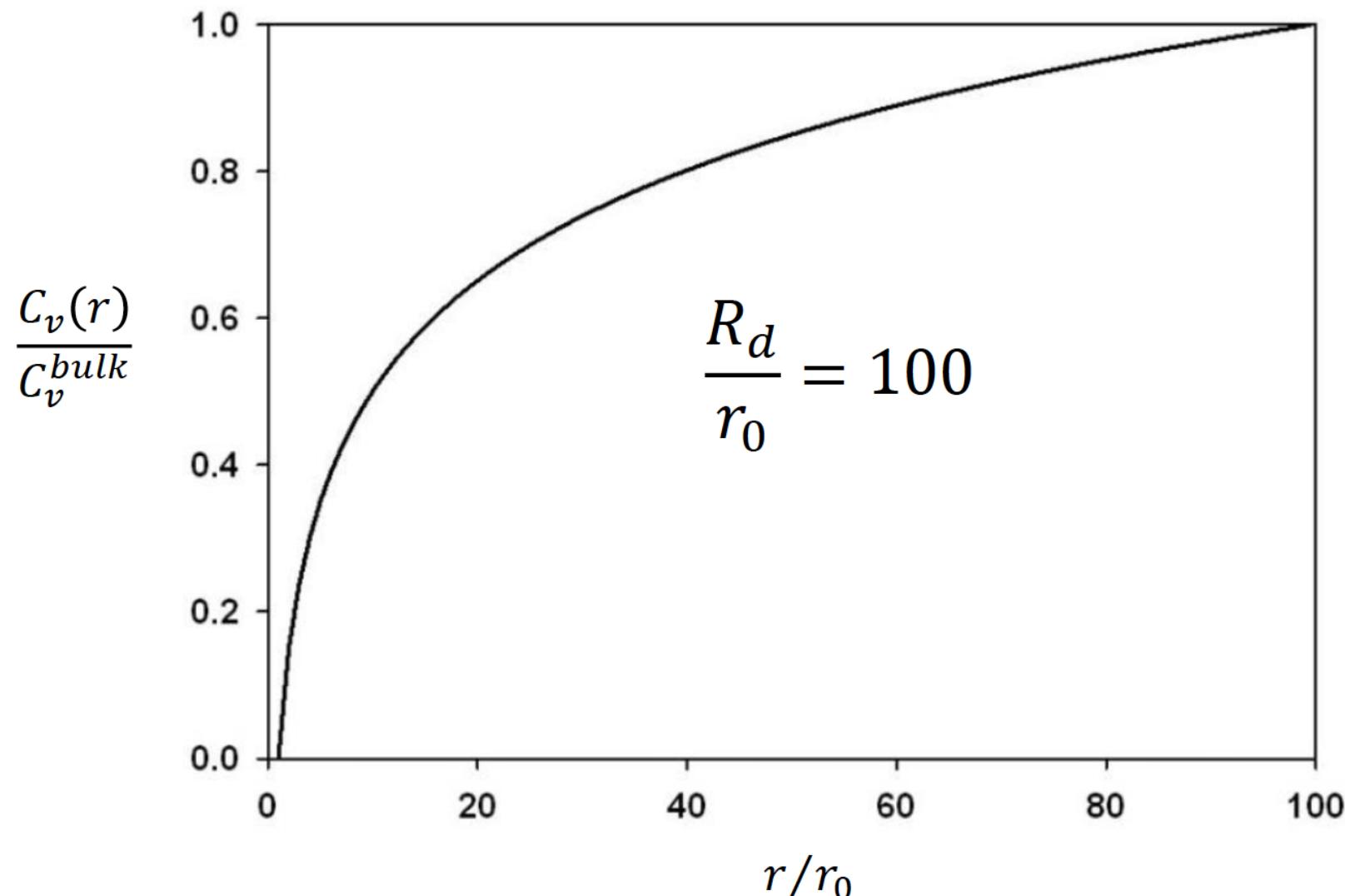
- The solution is then:

$$C_{i,v} = A \ln(r) + B$$

- Using the boundary conditions established by our assumptions:

- Gives us:

# Point Defect Absorption by Dislocations

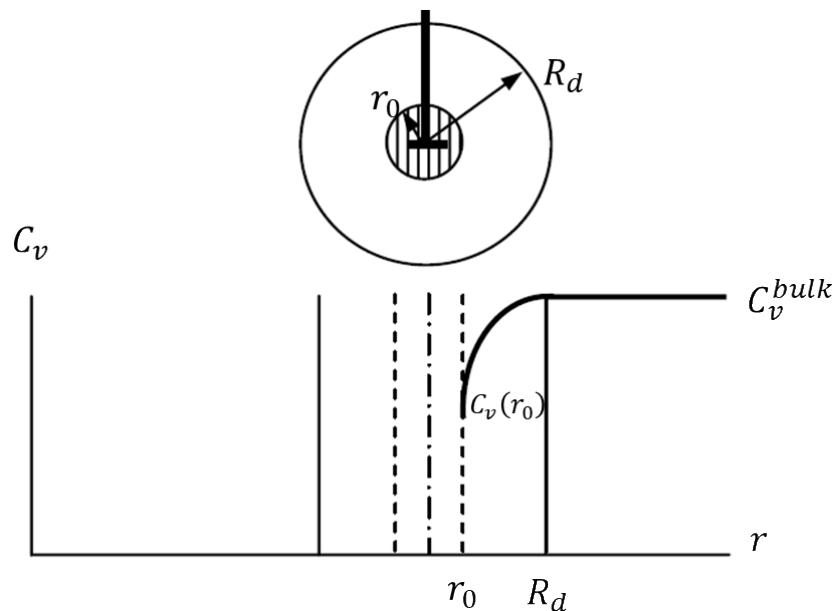


# Point Defect Absorption by Dislocations

We now need the rate of absorption per unit length of the dislocation, e.g. the flux to the line dislocation:

$$j^{disl} = \frac{\text{disl. surface area} \times \text{defect flux}}{\text{dislocation length}}$$

$$j^{disl} = \frac{2\pi r_o L \times \text{defect flux}}{L} = 2\pi r_o \times \text{defect flux}$$



The defect flux is dependent on the diffusion of the defects and their concentration, giving:

$$j^{disl} = 2\pi r_o D_{i,v} \left( \frac{dC_{i,v}}{dr} \right)_{r_o}$$



# Point Defect Absorption by Dislocations

- Now that we have:

$$j^{disl} = 2\pi r_o D_{i,v} \left( \frac{dC_{i,v}}{dr} \right)_{r_o}$$

- We can substitute our previous equation:

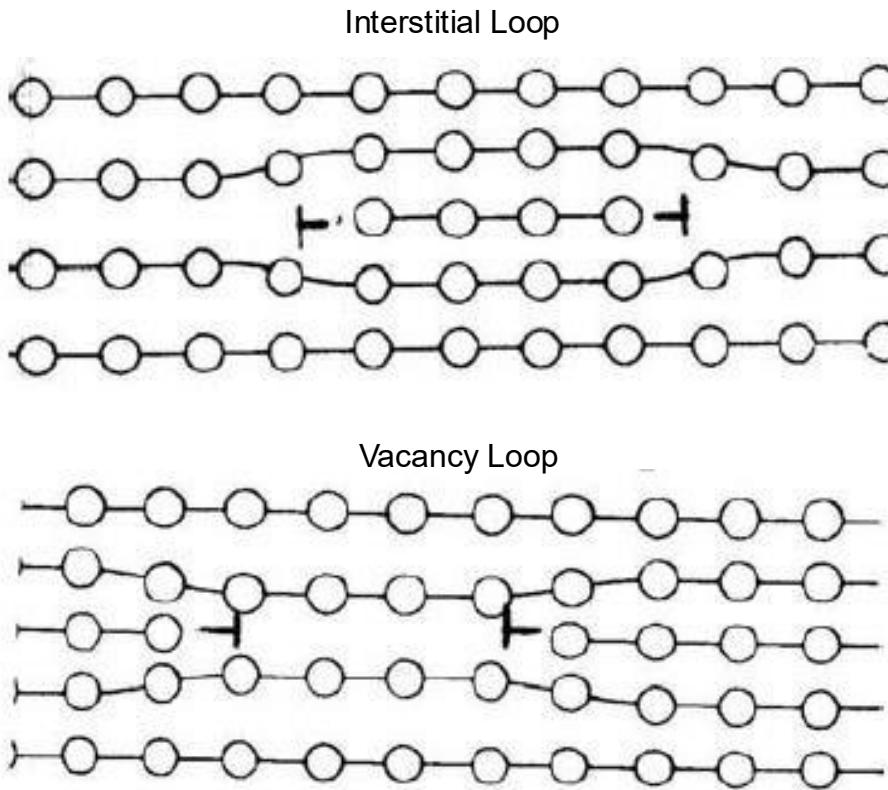
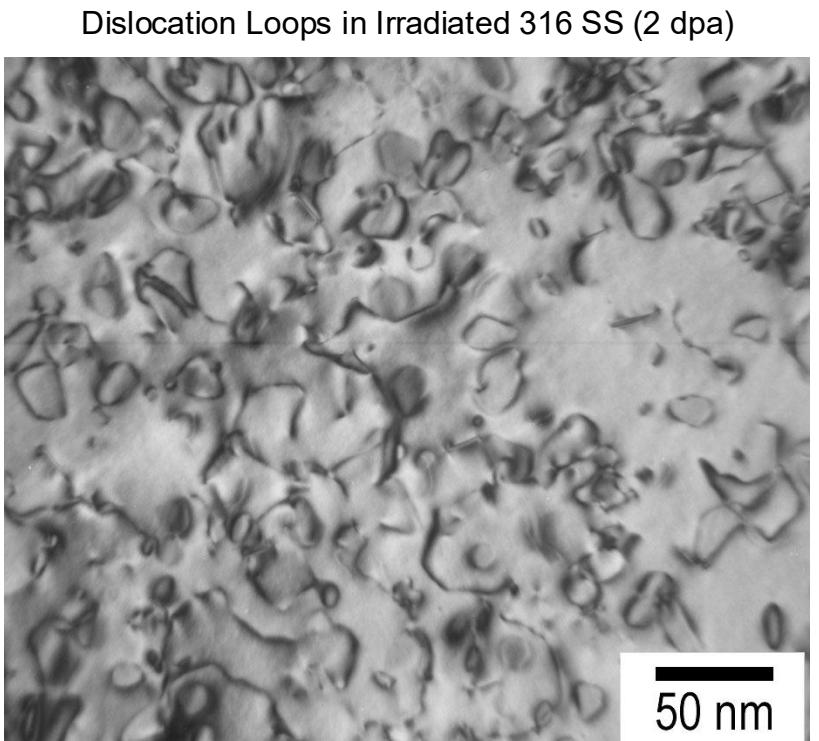
$$C_{i,v}(r) = C_{i,v}^{bulk} \frac{\ln \frac{r}{r_0}}{\ln \frac{R_d}{r_0}}$$

- Into the above giving:

$$j^{disl} = 2\pi D_{i,v} \frac{C_{i,v}^{bulk}}{\ln \frac{R_d}{r_0}}$$

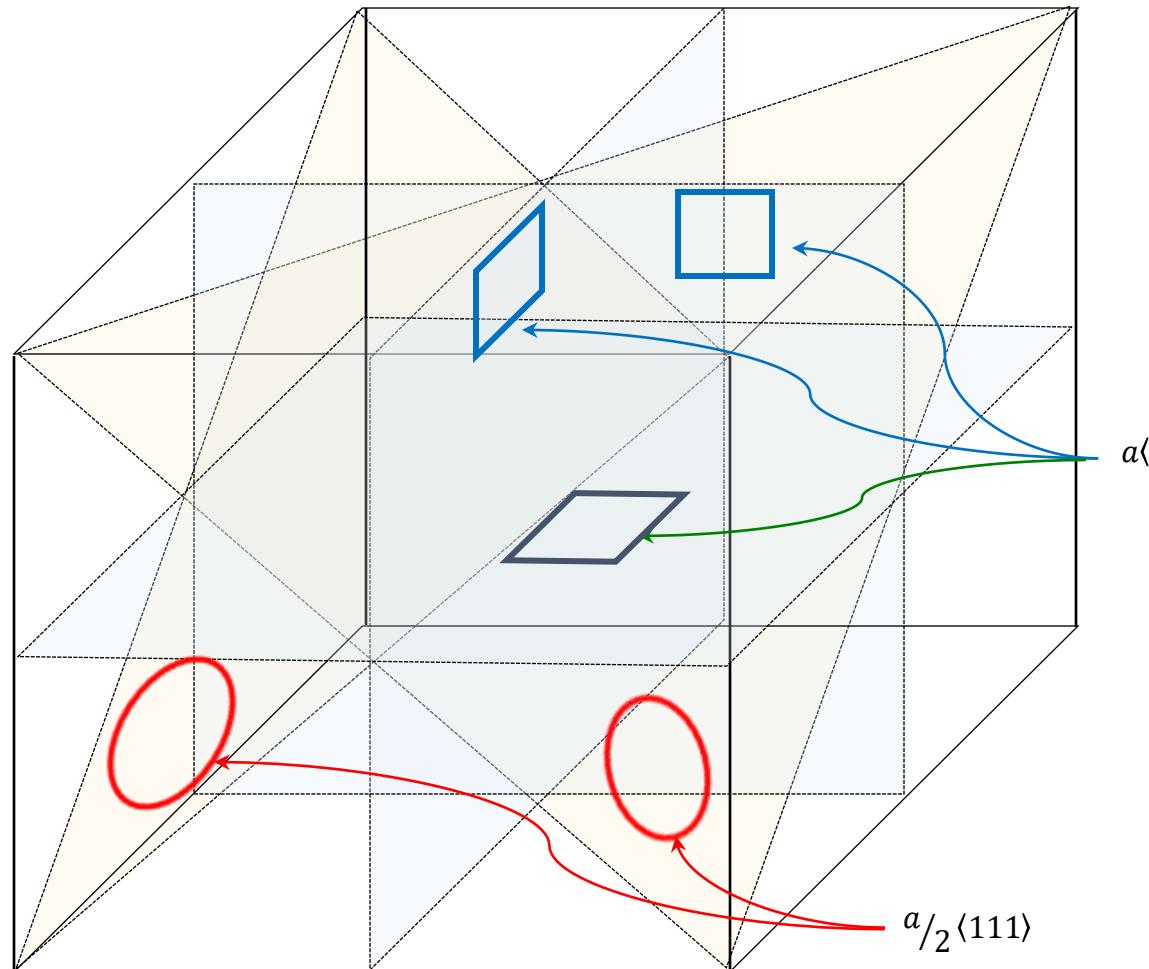
- Since there is **p<sub>d</sub>** cm of dislocation line per cm<sup>3</sup>:

# Accounting for dislocation loops

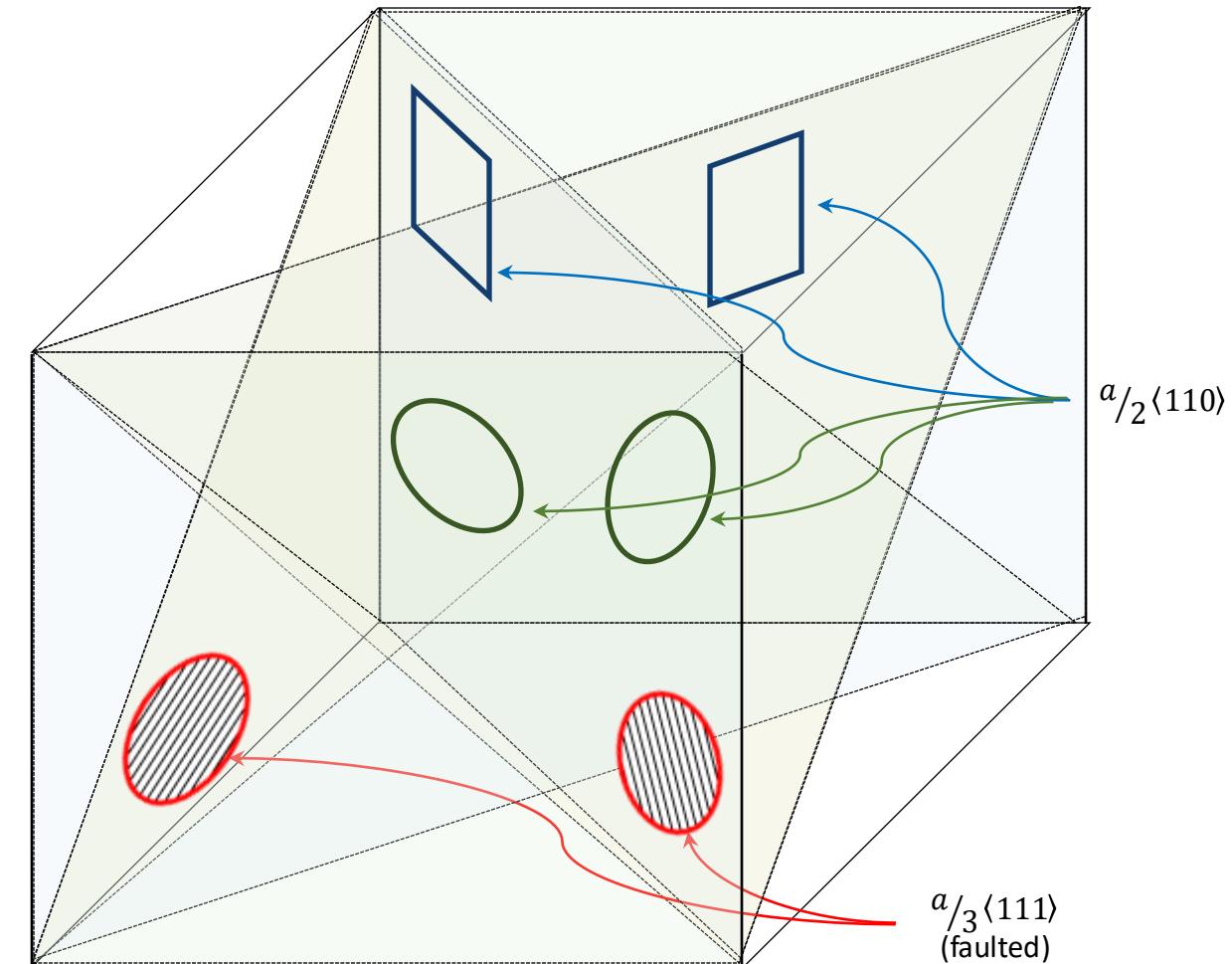


- Dislocation Loop: when a dislocation line forms a closed loop instead of extending until it reaches an interface
  - Character of the dislocation (edge, screw, mixed) changes continuously along the line
  - Loops typically grow

For most BCC and FCC materials the Burgers vector and habit plane are well known



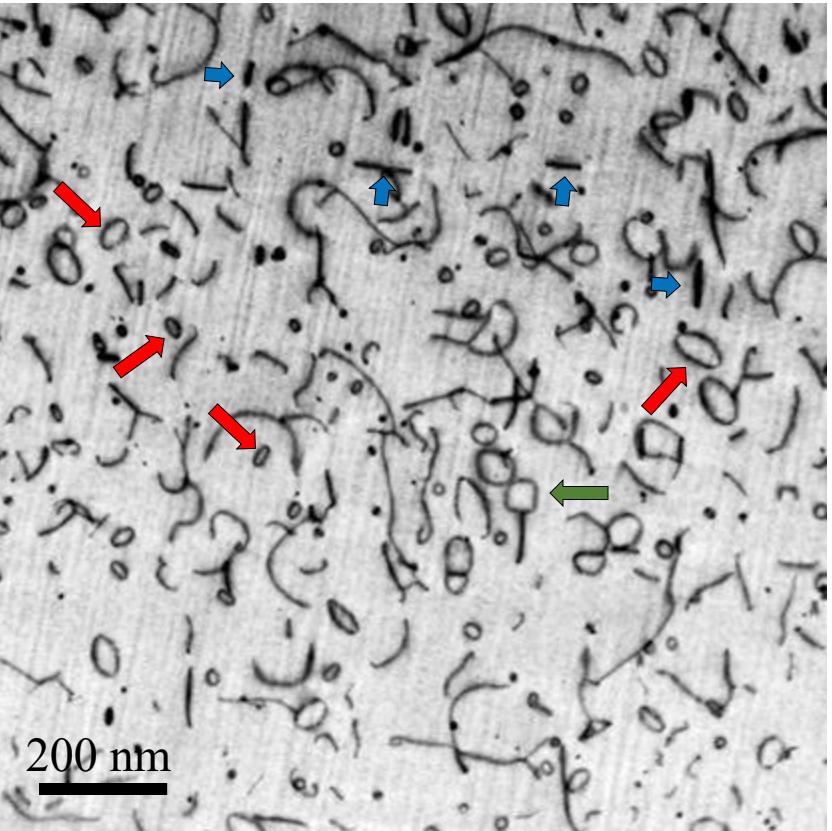
Body Centered Cubic  
(BCC)



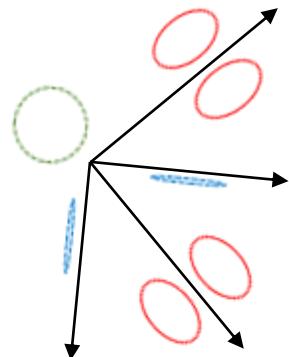
Face Centered Cubic  
(FCC)



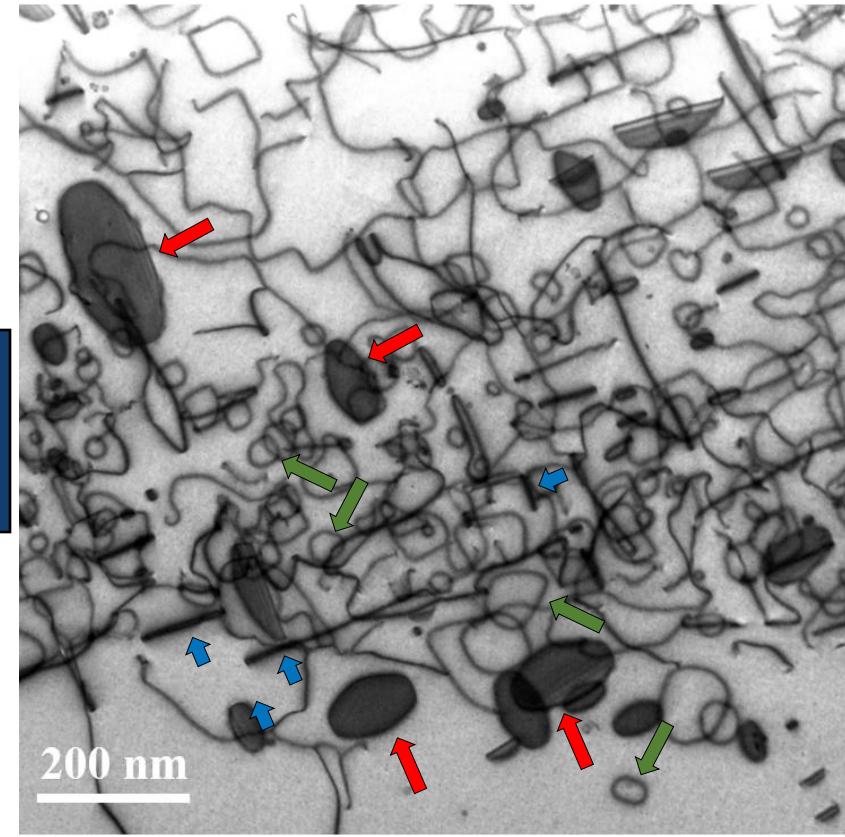
For most BCC and FCC materials the Burgers vector and habit plane are well known



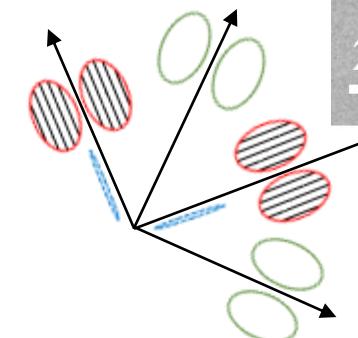
Body Centered Cubic  
(BCC)



Imaging down  
the [100] zone

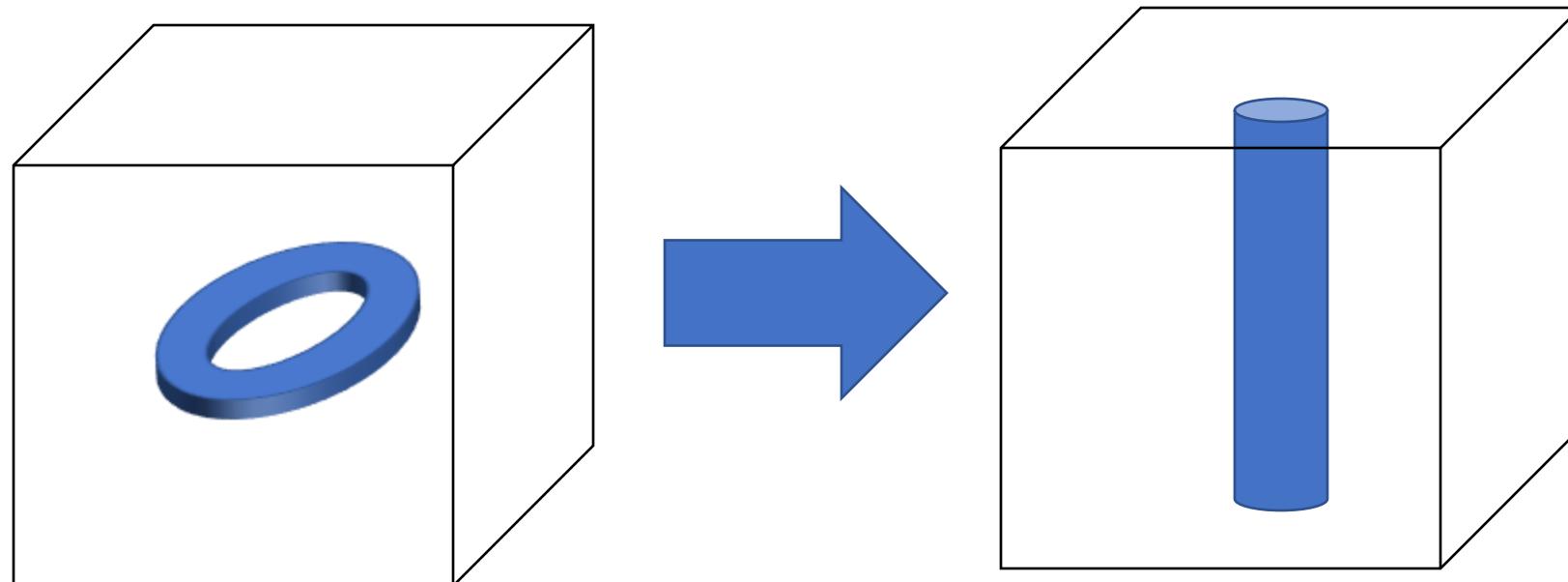


Face Centered Cubic  
(FCC)



# Accounting for dislocation loops

- We derived the reaction rate and sink strength for dislocation lines, but it is also used for dislocation loops. For loops  $p_d$  is used but with no consideration of geometry, e.g. the circular dislocation loops are effectively “straightened out”



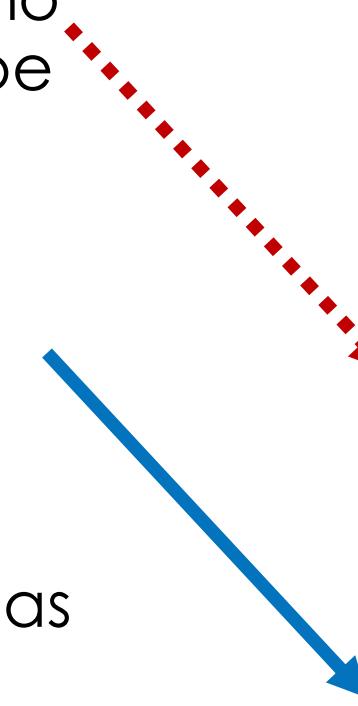
# Sink types

- Sinks can behave differently:

- **Neutral sinks:** Neutral sinks show no preference for capturing one type of defect over another.

- **Biased sinks:** Biased sinks show a preferential attraction for one defect over another.

- **Variable sinks:** Variable sinks act as traps for defects which hold the defect but preserve its identity until annihilation or it is released.

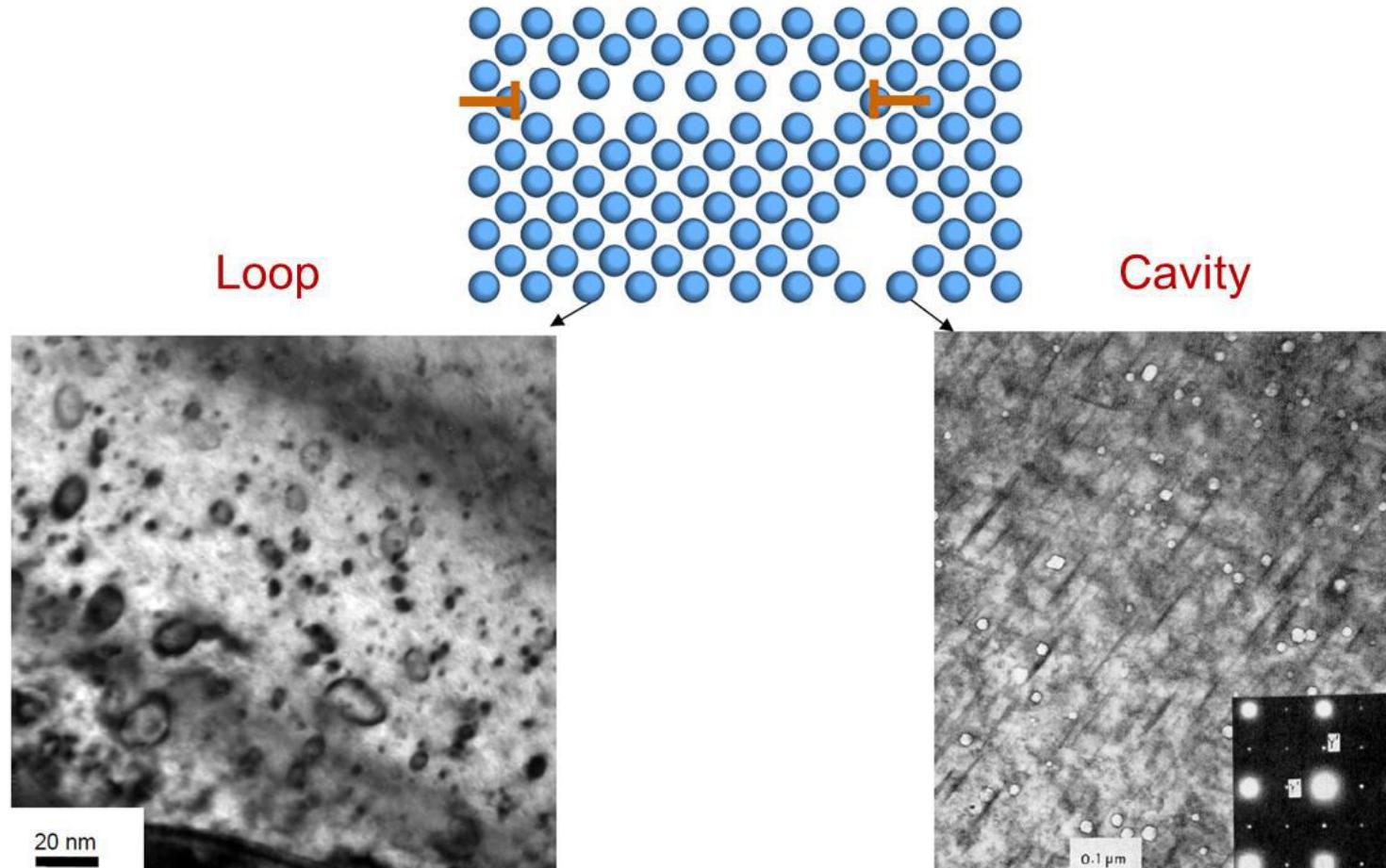


Coherent precipitates

Grain boundaries/Voids

Dislocations

# Sink Type II - Cavities



- Cavities are due to vacancies (and possibly gas atoms) diffusing and coalescing together within the matrix
- Can lead to brittle fracture (bad!)

# Sink Type II - Cavities

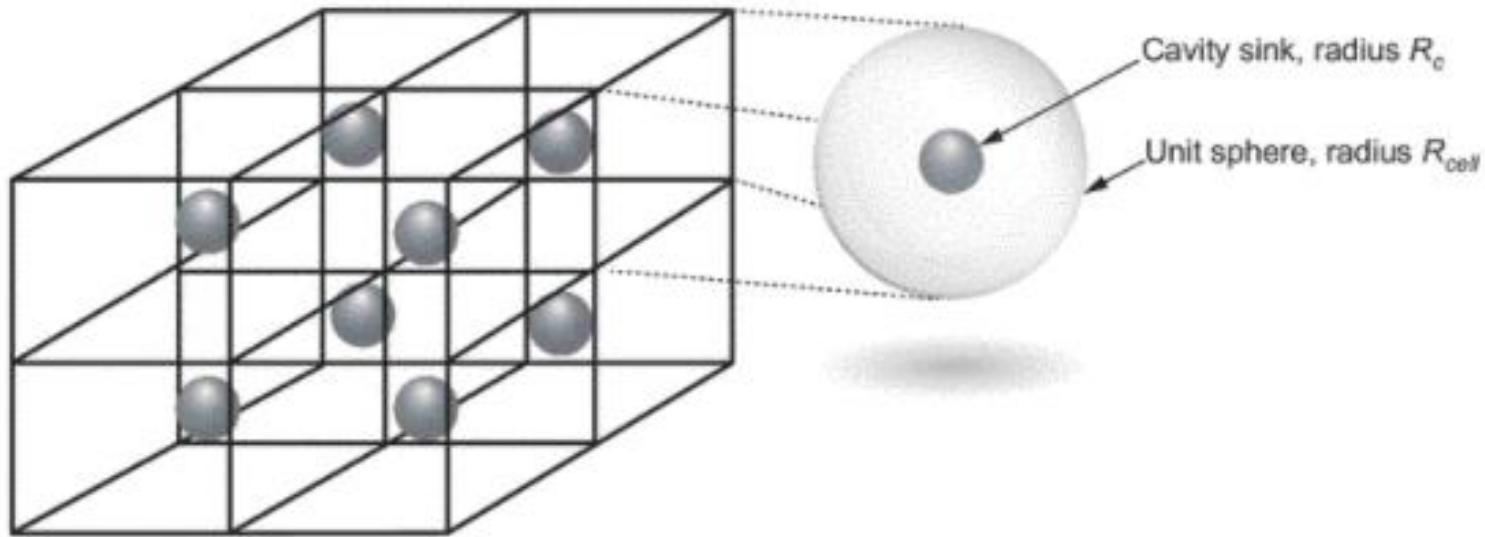
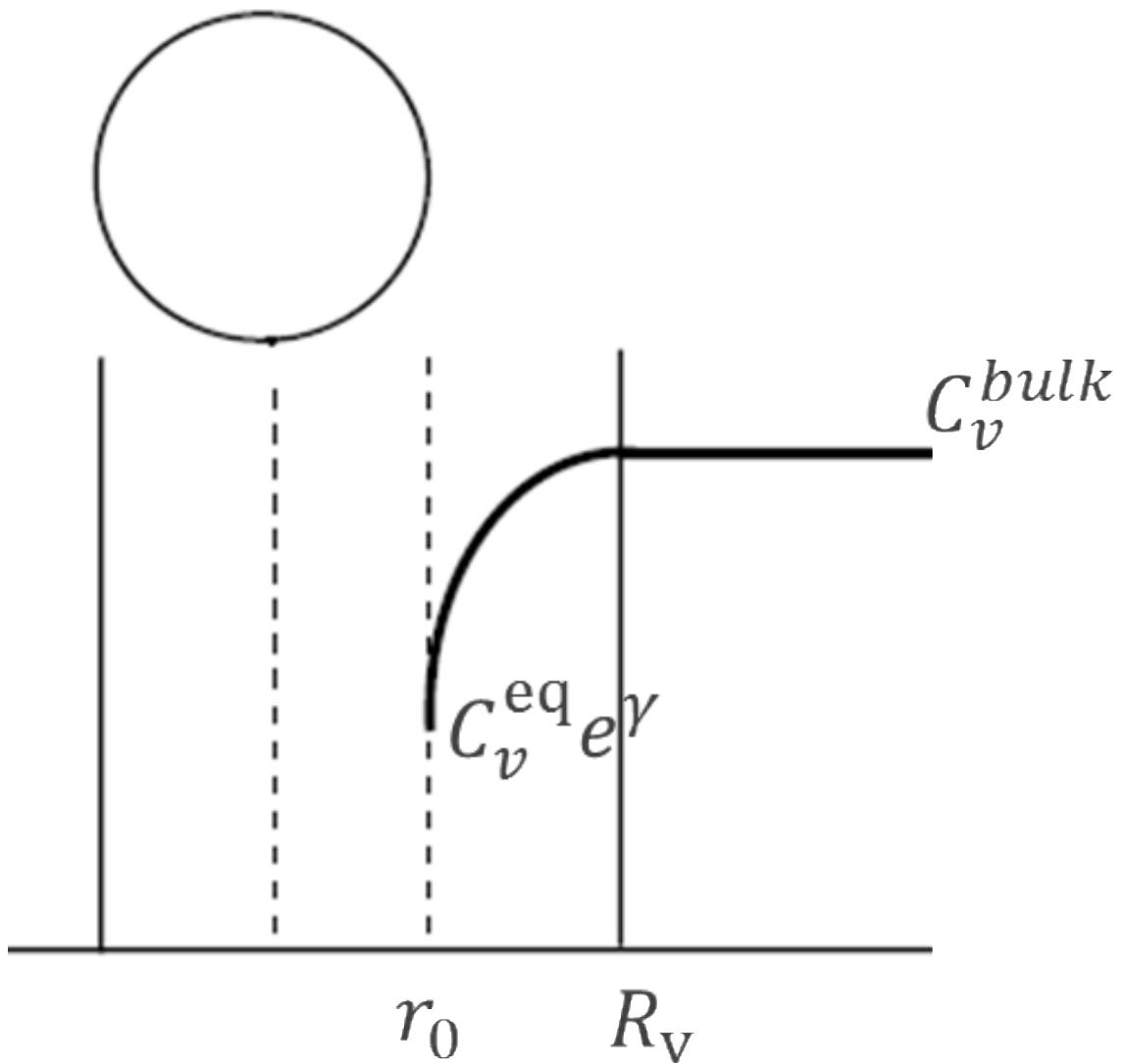


FIGURE 13.8: Spherical cavity sinks uniformly distributed in a solid. The cubes are unit cells for each sphere.

- Similar arguments for point defect absorption can be made in the case of voids:

$$\frac{1}{r^2} \frac{d}{dr} \left( r^2 \frac{dC_v}{dr} \right) = 0 \quad \rightarrow C_v(r) = -\frac{A}{r} + B$$

# Sink Type II - Cavities



It is assumed that the boundary conditions are:

In these conditions:

$$\frac{C_v(r) - C_v(r_o)}{C_v^{bulk} - C_v(r_o)} = 1 - \frac{r_o}{r}$$



# Sink Type II - Cavities

The rate of absorption per cavity is then given as:

$$j_{i,v}^{Cavity} = 4\pi r_o D_{i,v} C_{i,v}^{bulk}$$

Considering all cavities using  $N_c$  (cavities per unit volume), we get:

$$J_v^C = 4\pi r_o N_c D_v C_v^{bulk}$$

$$J_i^C = 4\pi r_o N_c D_i C_i^{bulk}$$

Then:

# Point Defect Kinetic Equations

- If we neglect clustering:

$$\frac{\partial C_v}{\partial t} = K_0 - K_{iv} C_i C_v - \sum_s K_{vs} C_v C_s + D_v \nabla^2 C_v$$

$$\frac{\partial C_i}{\partial t} = K_0 - K_{iv} C_i C_v - \sum_s K_{is} C_v C_s + D_i \nabla^2 C_i$$

- Example of defect absorption to cavities:

$$\frac{\partial C_v}{\partial t} = K_0 - K_{iv} C_i C_v - z_v p_d D_v C_v + 4\pi R_c N_c D_v C_v$$

$$\frac{\partial C_i}{\partial t} = K_0 - K_{iv} C_i C_v - z_i p_d D_i C_i + 4\pi R_c N_c D_i C_i$$

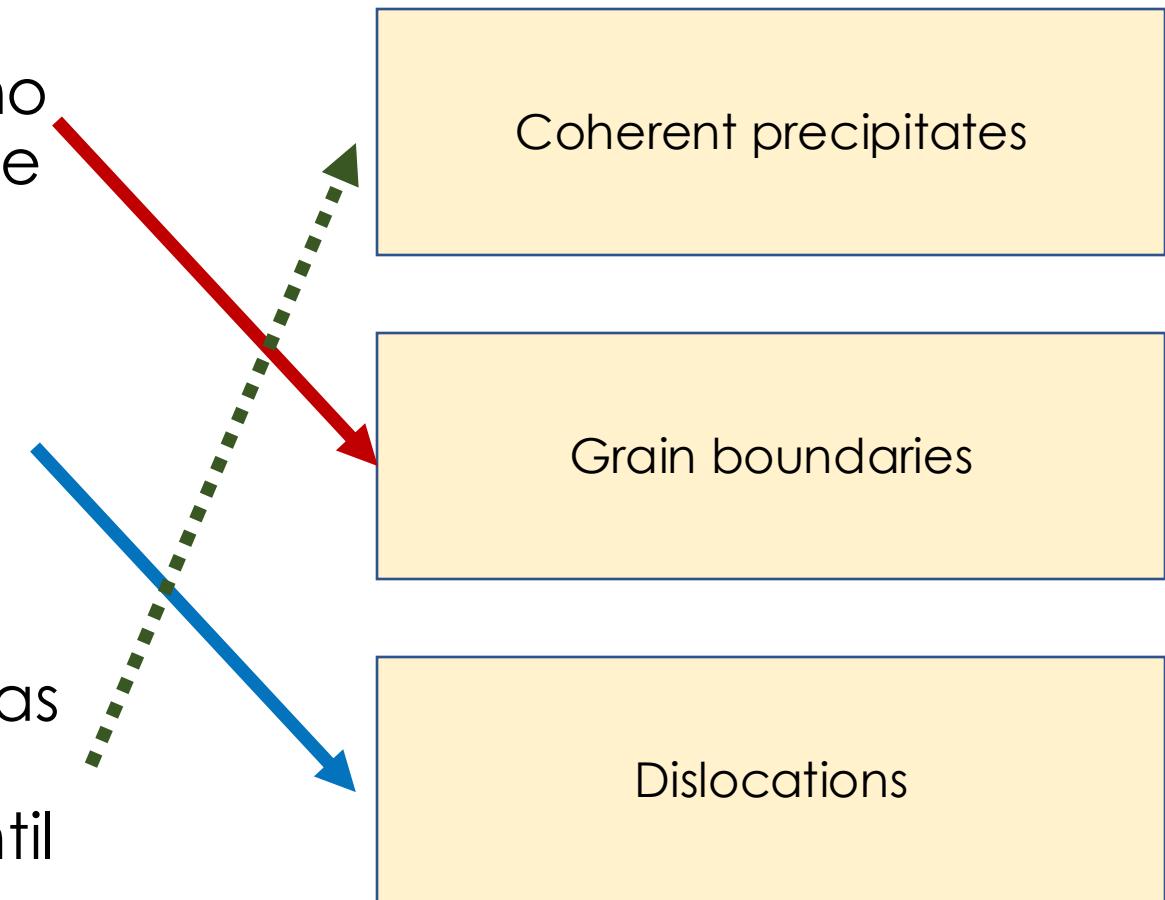
# Sink types

- Sinks can behave differently:

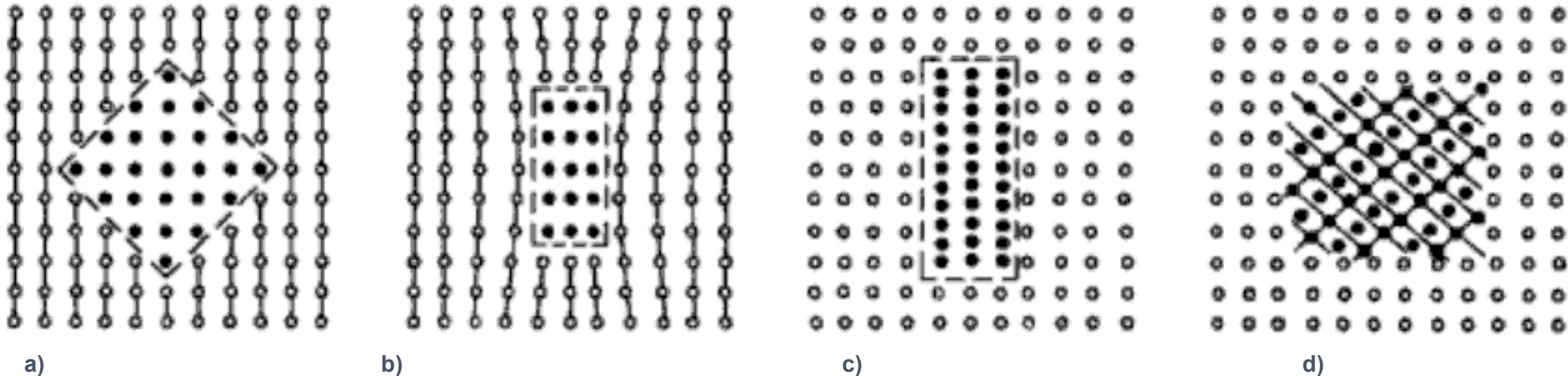
- **Neutral sinks:** Neutral sinks show no preference for capturing one type of defect over another.

- **Biased sinks:** Biased sinks show a preferential attraction for one defect over another.

- **Variable sinks:** Variable sinks act as traps for defects which hold the defect but preserve its identity until annihilation or it is released.



# Sink Type III – Coherent Precipitates (PPTs)



- Precipitates are the result of the local solubility limit being reached causing a new phase to form
- Precipitates can be either coherent, partially coherent or incoherent
  - Coherency: a perfect lattice match between the PPT and matrix
  - Coherency affects how dislocations interact with the PPT
  - Coherency can also affect diffusion in and around the PPT



# Sink Type III – Coherent Precipitates (PPTs)



- Precipitates impede dislocation motion
- Inclusion of precipitates can strengthen a material

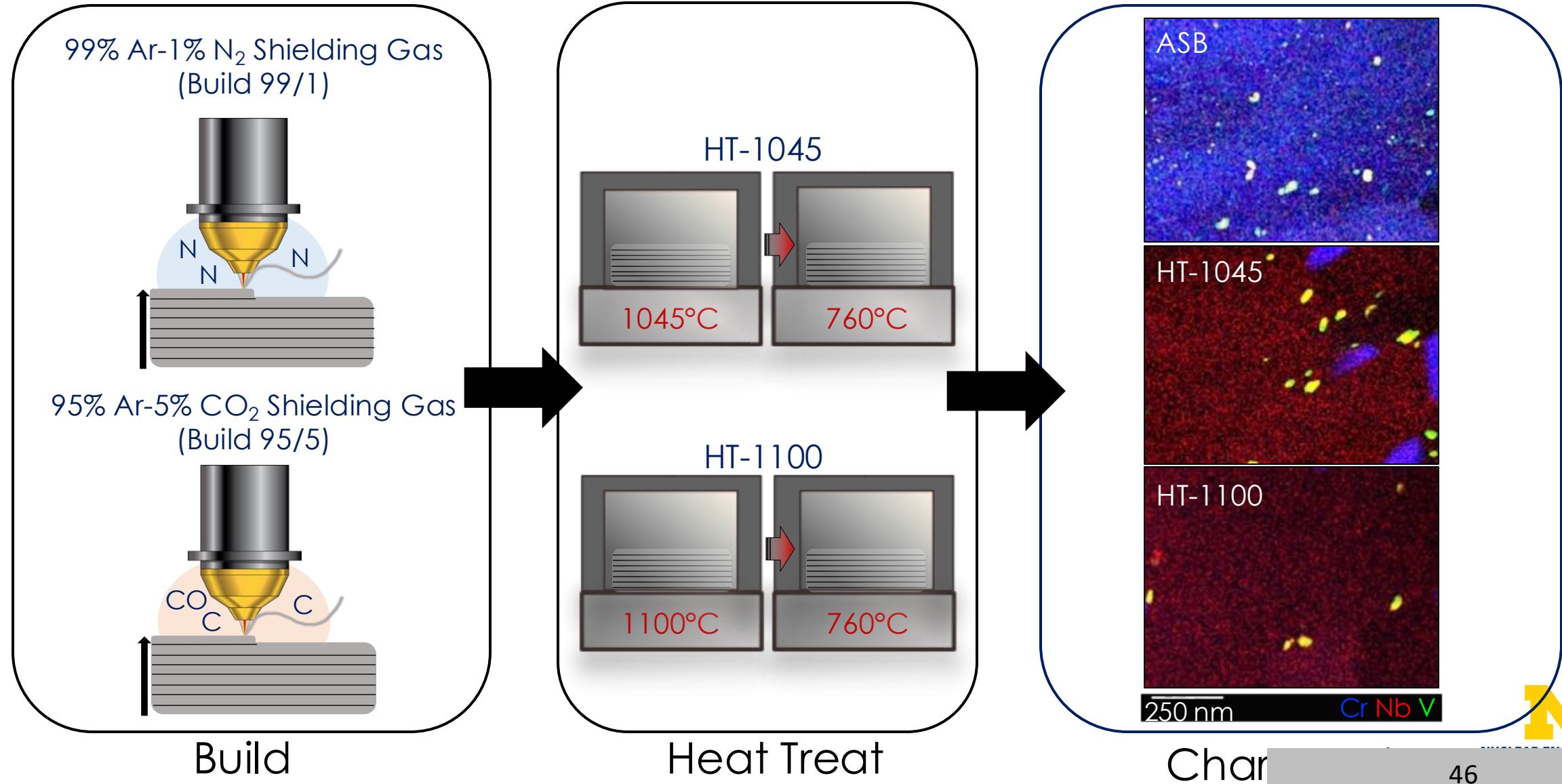
# Sink Type III – Coherent Precipitates (PPTs)

- Coherent precipitates act as traps
- Bias to interface depends on the other biased sinks present in the microstructure (such as dislocations!)
- Vacancies and interstitials reduce the strain field at the trap due to the lattice mismatch



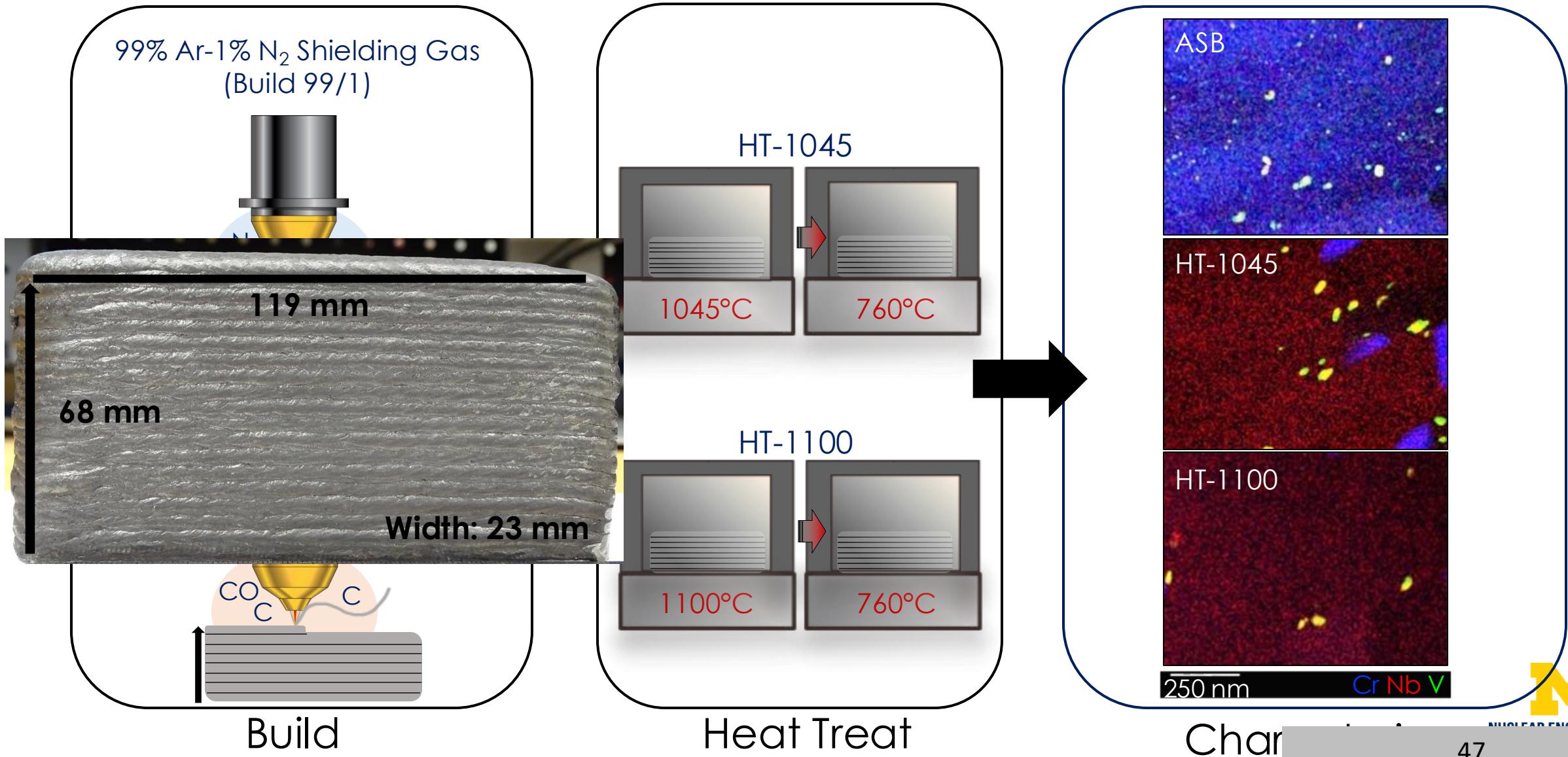
# WAAM Grade 91 Experimental Details

Control MX precipitate structure with C and N additions using different shielding gases



# Wire Arc AM Experimental Details

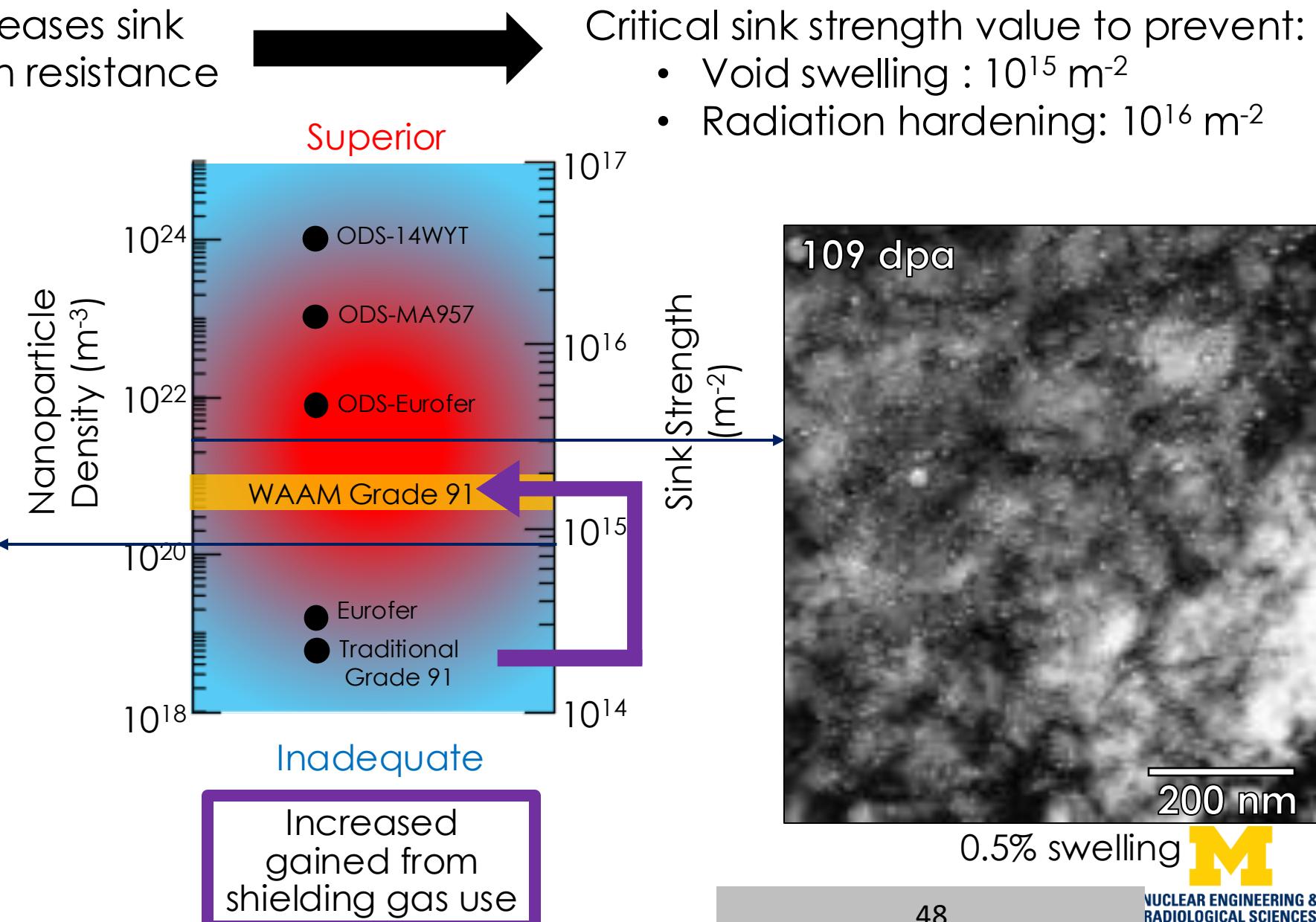
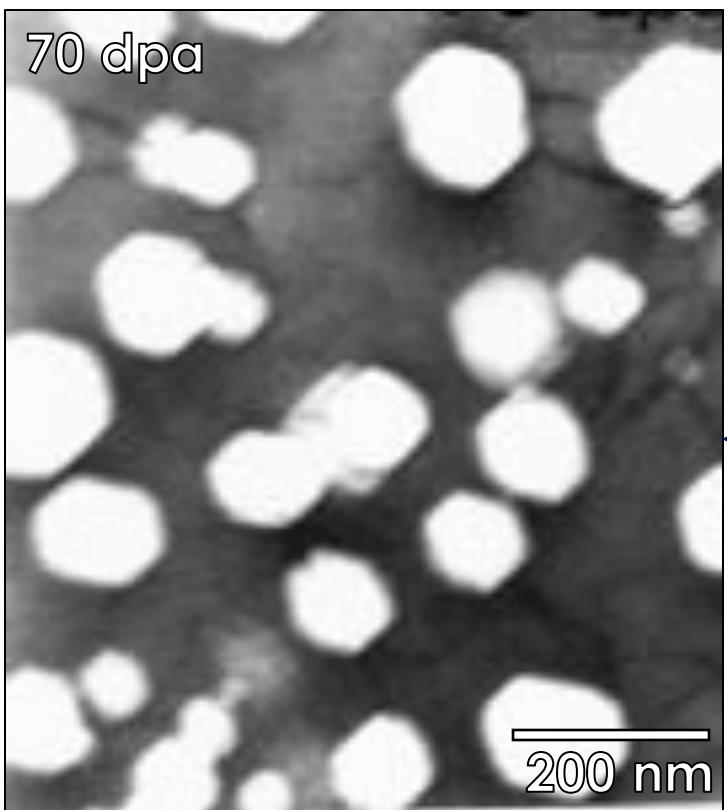
Control MX precipitate structure with C and N additions using different shielding gases



# Shielding Gas Effect on Sink Strength

Nanoscale precipitation increases sink strength and hence radiation resistance of a material

$$S_{\text{ppt}} \sim 4\pi RN$$



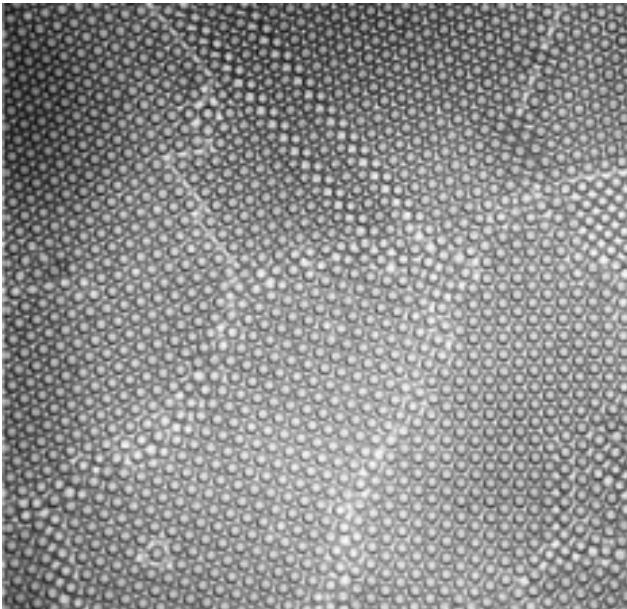
# Putting it together:

Table 5.2 Reaction rate constants for defect–sink reactions

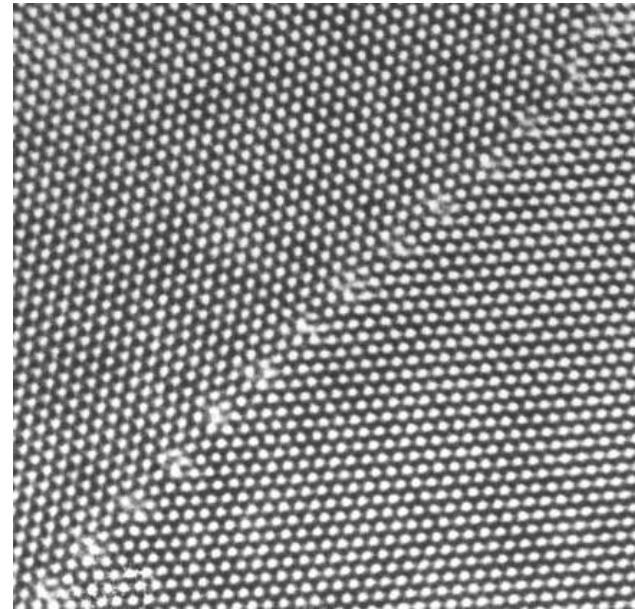
Reaction	Rate constant	Sink strength	Eq. #
v + v	$K_{2v} = \frac{z_{2v}\Omega D_v}{a^2}$	—	Equation (5.58)
i + i	$K_{2i} = \frac{z_{2i}\Omega D_i}{a^2}$	—	Equation (5.58)
v + i	$K_{iv} = \frac{z_{iv}\Omega D_i}{a^2}$	—	Equation (5.61)
<b>v, i + void</b>			
Reaction rate control	$K_{vv} = \frac{4\pi R^2 D_v}{a} \quad K_{iv} = \frac{4\pi R^2 D_i}{a}$	$k_{vv}^2 = k_{iv}^2 = \frac{4\pi R^2 \rho_v}{a}$	Equation (5.65)
Diffusion control	$K_{vv} = 4\pi R D_v \quad K_{iv} = 4\pi R D_i$	$k_{vv}^2 = k_{iv}^2 = 4\pi R \rho_v$	Equation (5.84)
Mixed rate control	$K_{vv} = \frac{4\pi R D_v}{1 + \frac{a}{R}} \quad K_{iv} = \frac{4\pi R D_i}{1 + \frac{a}{R}}$	$k_{vv}^2 = k_{iv}^2 = \frac{4\pi R \rho_v}{1 + \frac{a}{R}}$	Equation (5.102)
<b>v, i + dislocation</b>			
Diffusion control	$K_{vd} = \frac{2\pi D_v}{\ln(\mathcal{R}/R_{vd})} \quad K_{id} = \frac{2\pi D_i}{\ln(\mathcal{R}/R_{id})}$	$k_{vd}^2 = \frac{2\pi \rho_d}{\ln(\mathcal{R}/R_{vd})} \quad k_{id}^2 = \frac{2\pi \rho_d}{\ln(\mathcal{R}/R_{id})}$	Equations (5.99, 5.100)
Reaction rate control	$K_{vd} = z_{vd} D_v \quad K_{id} = z_{id} D_i$	$k_{vd}^2 = z_{vd} \rho_d \quad k_{id}^2 = z_{id} \rho_d$	Equation (5.67)
Mixed rate control	$K_{vd} = \frac{D_v}{\frac{1}{z_{vd}} + \frac{\ln(\mathcal{R}/R_{vd})}{2\pi}} \quad K_{id} = \frac{D_i}{\frac{1}{z_{id}} + \frac{\ln(\mathcal{R}/R_{id})}{2\pi}}$	$k_{vd}^2 = \frac{\rho_d}{\frac{1}{z_{vd}} + \frac{\ln(\mathcal{R}/R_{vd})}{2\pi}} \quad k_{id}^2 = \frac{\rho_d}{\frac{1}{z_{id}} + \frac{\ln(\mathcal{R}/R_{id})}{2\pi}}$	Equation (5.104)
<b>v, i + grain boundary</b>			
Diffusion control	$K_{vgb} = 4\pi D_v d \quad K_{igb} = 4\pi D_i d$ $K_{vgb} = \pi k D_v d^2 \quad K_{igb} = \pi k D_i d^2$	$k_{vgb}^2 = 24/d^2, \quad d < 10^{-3} \text{ cm}$ $k_{vgb}^2 = 6k/d, \quad d > 10^{-3} \text{ cm}$	Equation (5.115) Equation (5.116)
v, i + coherent ppt	$K_{vCP} = 4\pi R_{CP} D_v Y_v, \quad K_{iCP} = 4\pi R_{CP} D_i Y_i$	$k_{vCP}^2 = 4\pi R_{CP} \rho_{CP} Y_v, \quad k_{iCP}^2 = 4$	



# Sink Type IV – Grain Boundaries



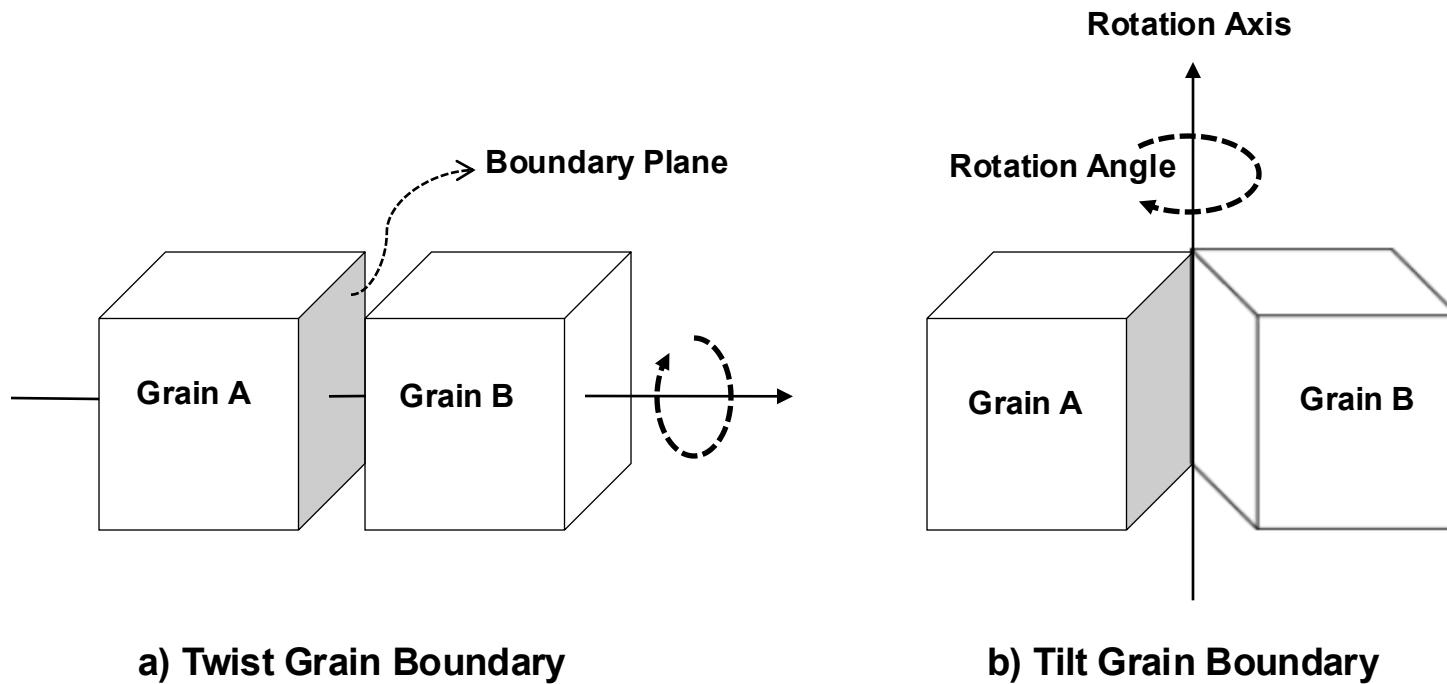
Bubble Raft Model of Grain Boundaries



HRTEM image of a  $\Sigma 19$  GB in Al

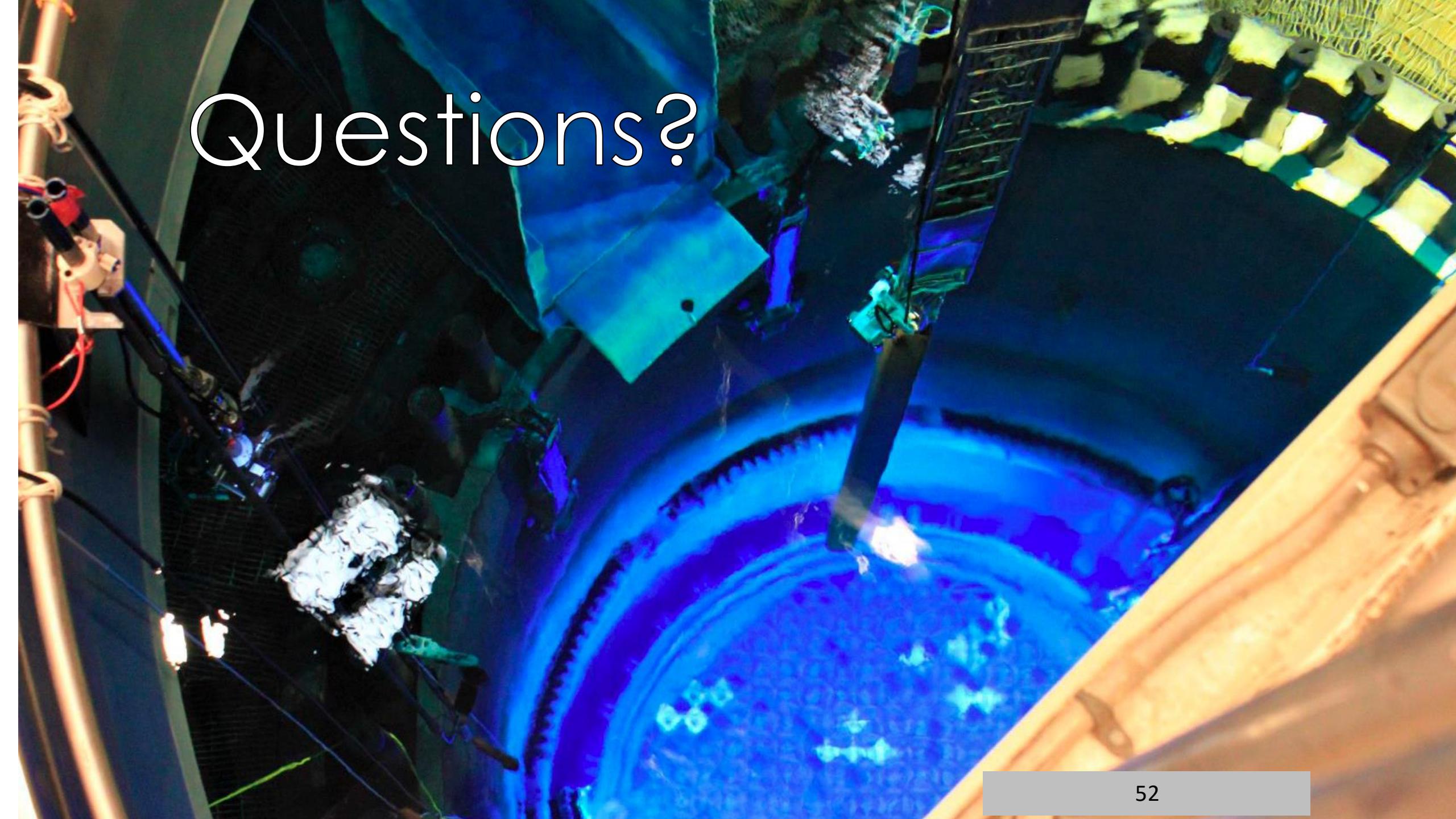
- A Grain Boundary is a general planar defect that separates regions of different crystalline orientation (i.e. *grains*) within a polycrystalline solid
- Grain boundaries can affect creep strength, yield strength, and diffusion

# Sink Type IV – Grain Boundaries



- Grain boundaries can have twist, tilt, or mixed character
- Variations in the degree of misalignment between two adjacent grains are possible





# Questions?